# FUJITSU MICROELECTRONICS PRODUCT GUIDE

# 2008.1 Product Guide





THE POSSIBILITIES ARE INFINITE

### **Technical Documentation of Electronic Devices**



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\* : SPANSION <sup>™</sup> Products

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### **ASSP Product Line-up**

### ASSP Product Line-up



# **Telephone Products**



### Telephone Products

### ISDN Digital Telephone LSIs

Part number	Functions	CODEC	Power supply voltage (V)	Package QFP
MB86434	AIU for ISDN digital telephones CODEC, DTMF tones, service tone Internal ringer tone	A-laW μ-laW 14-bit linear	+5±5%	64P

Package: P - Plastic

#### LSIs for Digital Mobile Telephones

Part number	Functions	Compression law	Bower supply voltage ()/)	Package
Faithumber	Functions	Compression law	rower supply voltage (v)	LQFP
MB86435	2 V single power supply All I	A-laW	2.7 to 2.6	64P
MB86437		linear	2.7 10 3.0	48P

Package: P - Plastic



#### **PLL Frequency Synthesizers**

Part number		out iency (Hz)	PLL		Divide	e ratio		Power supply current	Power save current	Power supply voltage (V)			Package	
	min	max	Type	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	<b>typ</b> (μ <b>Α</b> )	min	typ	max	всс	TSSOP
MB15E07SB	100M	256		32/33,				8.0	0.1	2.7	3.75	5.0	16P	16P
WE ISEO/ OIT	100101	2.50		64/65	64/65			7.0	0.1	2.7	3.0	5.0	101	101
MB15E06SR	700M	3.0G	Integer -N	64/65, 128/129	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	8.0	0.1	2.7	3.0	4.0	16P	16P
MB15E05SB	300M	2.00		64/65,				7.0	0.1	2.7	3.75	5.0	16P	16P
WD IJE033H	500101	2.00		128/129				6.0	0.1	2.7	3.0	5.0	IUF	IUF
											Р	ackac	ie: P -	Plastic

Binary

11bit

3 to 2047

64/65,

128/129

1.2G

Single Integer-N PLL

MB15E03SL

Power supply voltage Input Power Power frequency **Divide ratio** Package supply save band (Hz) PLL (V) Part number current Туре **typ** (μ**A**) Prescal typ (mA) Program Swallow Reference min max min typ max SSOP BCC counter counter counter er Binary Binary 32/33, Binary 7bit MB15E07SL 700M 2.5G 11bit 14bit 4.5 0.1 2.4 3.0 3.6 16P 16P 64/65 0 to 127 3 to 2047 3 to 16383 Binary Binary 64/65, Binary 7bit Integer MB15E05SL 2.0G 11bit 14bit 3.5 0.1 2.4 3.0 3.6 16P 16P -N 128/129 0 to 127 3 to 2047 3 to 16383 100M

Binary 7bit

0 to 127

Binary

14bit

3 to 16383

2.5

0.1

2.4 3.0 3.6

Package: P - Plastic

16P

16P

(Continued)	(Continued)								
		lr ba	nput frequency and of prescaler	Ρ	LL type	Prescaler divide ratio		Part number	Features
	Dual		400 MHz to 2.6 GHz	RF	Integer-N	32/33, 64/65		MB15F78UL	For digital telecommunica- tions equipment
	Integer-N PLL		100 MHz to 1.2 GHz	IF	Integer-N	16/17, 32/33			Low noise Low power dissipation
		] .							
			2.0 GHz to 6.0 GHz	RF	Integer-N	6.0G : 16/17, 32/33	-	MB15F76UL	For digital high-speed tele-
			100 MHz to 1.5 GHz	IF	Integer-N	1.5G : 4/5, 8/9			communications equipment
					(Fixed	l part 4 division)			
					•			r	
			2.0 GHz to 4.0 GHz	RF	Integer-N	4.0G : 64/65, 128/129		MB15F74UV	Small Package For digital high-speed telecom-
			200 MHz to 2.0 GHz	IF	Integer-N	2.0G : 32/33, 64/65			munications equipment
								MB15F74UL	For digital high-speed tele- communications equipment
		Ι.							
			200 MHz to 2.25 GHz	RF	Integer-N	2.25G : 64/65, 128/129		MB15F73UV	Small Package For digital high-speed telecom-
			50 MHz to 600 MHz	IF	Integer-N	600M : 8/9, 16/ 17			munications equipment
								MB15F73UL	For digital high-speed tele- communications equipment
			100 MHz to 1.3GHz	RF	Integer-N	1.3G : 64/65, 128/129		MB15E72UV	Small Package
			50 MHz to 350 MHz	IF	Integer-N	350M : 8/9, 16/ 17			munications equipment
								MB15F72UL	For digital high-speed tele- communications equipment
			500 MHz to 2.6 GHz	RF	Integer-N	32/33, 64/65		MB15E30LIV	Small Package For digital high-speed telecom-
			45 MHz to 510 MHz	IF	Integer-N	8/9, 16/17			munications equipment Low power dissipation
			100 MHz to 1.1GHz	RF	Integer-N	1.1G : 64/65, 128/129		MB15F07SI	For digital high-speed telecom-
			100 MHz to 1.1GHz	IF	Integer-N	1.1G : 64/65, 128/129			Low noise
					Integer-N Sigma-De	Integer-N tec: Ita:Sigma-Delta	hno frao	ology ctional-N technol	logy

(Continued)

(Continued)

Dual Integer-N PLL

Part number	In frequ band	put Jency I (Hz)	PLL		Divide ra	itio		Power supply current	Power save current	Pow v	er su oltag (V)	pply e	Pac	kage
	min	max	туре	Prescaler	Program counter	Swallow counter	Referenc e counter	typ (mA)	<b>typ</b> (μ <b>Α</b> )	min	typ	max	всс	TSSOP
MB15F74UV	2.0G 200M	4.0G 2.0G		RF : 64/65, 128/129 IF : 32/33, 64/65	Binary	Piport	Binary	6.5 2.5	0.1 0.1	2.7	3.0	3.6	18P	_
MB15F73UV	200M 50M	2.25G 600M		RF: 64/65, 128/129 IF:8/9, 16/17	11 bit 3 to	7bit 0 to 127	14bit 3 to	2.0 1.2	0.1 0.1	2.4	2.7	3.6	18P	-
MB15F72UV	100M 50M	1.3G 350M		RF : 64/65, 128/129 IF : 8/9, 16/17	2047	0.00.121	16383	1.5 1.0	0.1 0.1	2.4	2.7	3.6	18P	-
MB15F30UV	500M 45M	2.6G 510M		RF : 32/33, 64/65 IF : 8/9, 16/17	Binary 11 bit 3 to 2047	Binary 7bit 0 to 63	Binary 15bit 3 to 32768	2.8 1.2	0.1 0.1	2.4	2.7	3.6	18P	_
MB15F78UL	400M 100M	2.6G 1.2G	Integer	RX : 32/33, 64/65 TX : 16/17, 32/33	Binary 11 bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	2.8 1.7	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F76UL	2.0G 100M	6.0G 1.5G	-N	RF : 16/17, 32/33 (Fixed part 4 division) IF : 4/5, 8/9 (Fixed part 4 division)	Binary 13bit 3 to 8191	Binary 5bit 0 to 31	Binary 14bit 3 to 16383	6.2 2.3	0.1 0.1	2.5	3.0	3.6	20P	_
MB15F74UL	2.0G 200M	4.0G 2.0G		RF : 64/65,128/129 IF : 32/33,64/65	Diagant	Diagan	Binary	6.5 2.5	0.1 0.1	2.7	3.0	3.6	20P	-
MB15F73UL	200M 50M	2.25G 600M		RF : 64/65,128/129 IF : 8/9,16/17	Binary 11bit 3 to 2047	7bit 0 to 127	14bit 3 to	2.0 1.2	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F72UL	100M 50M	1.3G 350M		RF : 64/65,128/129 IF : 350M: 8/9,16/17		0.00.121	16383	1.5 1.0	0.1 0.1	2.4	2.7	3.6	20P	20P
MB15F07SL	100M 100M	1.1G 1.1G		64/65,128/129 64/65,128/129	Binary 11bit 3 to 2047	Binary 7bit 0 to 127	Binary 14bit 3 to 16383	5.5 5.5	0.1 0.1	2.5	3.0	3.6	16P	16P

Package: P - Plastic

#### (Continued) (Continued)



Single Sigma-Delta Fractional-N PLL

Part number	Inp frequ band	out iency (Hz)	PLL		Divide	ratio		Power supply current typ	Power save current	Power s volta (V		ipply je	Pack age
	min	max	Type	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	<b>typ</b> (μ <b>Α</b> )	min	typ	max	всс
MB15E65UV	100 M	2.0 G	Sigma-	16/17/18	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.6	0.1	2.7	3.0	3.3	18P
MB15E64UV	1.0 G	3.5 G	Delta	16/17/18	Binary 8 bit 9 to 255	Binary 4 bit 0 to 15	Binary 6 bit 1 to 63	4.6	0.1	2.7	3.0	3.3	18P

Package: P - Plastic

• Single Sigma-Delta Fractional-N PLL (RF) & Integer-N PLL (IF)

Part number	Inp frequ band	out iency (Hz)	PLL		Divid	e ratio		Power supply current	Power save current	l s vol	Powe supp tage	er ly (V)	Pack age
	min max	туре	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	<b>typ</b> (μΑ)	min	typ	max	всс	
MB15F63UL	100M 100M	2.0G 600M	Sigma -Delta, Integer -N	RF : 16/17, 20/21, IF : 8/9,16/17	Binary 7bit 5 to 127(RF) Binary 11bit 3 to 2047(IF)	Binary 4bit 0 to 15(RF) Binary 7bit 0 to 127(IF)	Binary 6bit 1 to 63(RF) Binary 14 bit 3 to 16383(IF)	6.1 1.4	0.1 0.1	2.7	3.0	3.3	20P

Package: P - Plastic

• IF Band Integer-N PLL

Part number	Inp frequ band	out ency (Hz)	PLL		Divid	e ratio		Power supply current typ	Power save current	Pow vol	ower supply voltage (V)		vly /) Package	
	min max		туре	Prescaler	Program counter	Swallow counter	Reference counter	typ (mA)	<b>typ</b> (μ <b>Α</b> )	min	typ	max	TSSOP	
MB15C101	233 259	.15 .20	Integer- N	16/17	291 33	7 12	384 40	1.0	-	2.4	3.0	3.6	8P	
MB15C02	10 M	330M	Integer- N	64/65	12bit, 5 to 4095	6bit, 0 to 63	14bit, 16 to 16383	1.0	70	1.0	1.2	1.5	16P 20P	

Package: P - Plastic



Specific power saving communication

Part number	Application	Frequency band	Functions	Power supply current	Power save current	Power supply voltage (V)			Package
		(10112)		typ (mA)	<b>typ (μΑ)</b>	min	typ	max	LQFP
MB15H121	Telemeter telecontroller security	430	Prescaler divide ratio 8/9 PA, Σ∆PLL, FSK-MOD, LNA, MIXER, LIMAMP, RSSI, FSK-DEM, VCO TANK circuit (internal)	6.7 (PLL) 23.0 (TX) 5.0 (RX)	0.3	2.2	2.5	2.8	48P

Package: P - Plastic

Semicustom IF PLL

	Frequency		Power	Comparison	Swallow	Reference	Power	Package	
Part number (Series name)	band (MHz)	Prescaler divide ratio	supply current (mA)	counter divide ratio (N)	counter divide ratio (A)	counter divide ratio (R)	supply voltage (V)	SSOP	BCC
MB15C100 series	to 300 * <sup>1</sup> (2.4 to 3.6 V) to 380 * <sup>1</sup> (2.4 to 3.0 V) to 500 * <sup>2</sup> (2.4 to 3.6 V)	8/9, 16/17, 32/33	1.2 (300 MHz, V <sub>CC</sub> = 3 V)	Any value between divide-by-5 and divide- by-4095	Any value between divide-by-0 and divide- by-31	Any value between divide-by-5 and divide- by-4095	+2.4 to +3.6	8P	16P (Stype)

\*1: Input sensitivity –10 to +2 dBm \*2: Input sensitivity –5 to +2 dBm

Package: P - Plastic

(Continued) Application Part number Features CDMA, GSM, Compact type with wide variable frequency Single Type VCO \* VC-90 series PCS, PHS band (700 MHz to 2500 MHz) Ultra Compact type with wide variable fre-V10x series quency band CDMA. PCS. Compact dual band type with band selection Dual Type V08 series GSM function (800 MHz to 2500 MHz) Compact dual band type with band selection V09 series function Transmitter Built in Duplexer, PowerAmp and Band Pass CDMA Single Type T021 series Module \* (CELL band) Filter (824MHz to 849MHz) Size (mm) Part number Correspondence system SAW D6CZ series US-PCS/W-CDMA II  $5.0 \times 5.0$ Duplexer \* 3.8 imes 3.8D5CF series CDMA/W-CDMA V  $3.0 \times 2.5$ D5GA series CDMA/W-CDMA V D5GC series J-CDMA (27MHz) D5GG series J-CDMA (6MHz) D6GZ series US-PCS/W-CDMA II 2.5 imes 2.0D5JB series CDMA/W-CDMA V

(Continued)

\*: Product of FUJITSU MEDIA DEVICES LIMITED

#### VCO

Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
VC-90 series			700 to 2500	25 to 22	$5.0 \times 4.0 \times 1.55$
V10x series	Voltege Controlled	CDIWA, COW, FCO, FTIO	700 10 2300	2.5 10 5.5	$4.5\times3.2\times1.5$
V08 series	Oscillator		800 to 2500	2.9	$5.5\times4.8\times1.8$
V09 series		CDMA, FC3, G3M	800 10 2300	2.0	$5.0\times4.0\times1.4$

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#### **Transmitter Module**

Part number	Functions	Application	Frequency (MHz)	Power supply voltage (V)	Package Typ. (mm)
T021 series	Built in Duplexer, PowerAmp and Band Pass Filter	CDMA (CELL band)	824 to 849	3.4	8.0 × 5.0 × 1.4

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#### SAW Duplexer for Mobile Communication System

Correspondence system	Size (mm)	Part Number	Remarks
	<b>3.8</b> imes <b>3.8</b>	FAR-D5CF-881M50-D1F1	Two types of package are available
CDMA/W-CDMA V	3.0  imes 2.5	FAR-D5GA-881M50-D1AA	Two types of package are available
	$2.5\times2.0$	FAR-D5JB-881 M50-D3AA	Two types of package are available
J-CDMA (27MHz)	3.0  imes 2.5	FAR-D5GC-911M50-D1CA	-
J-CDMA (6MHz)	3.0  imes 2.5	FAR-D5GG-872M00-D1GA	-
	5.0  imes 5.0	FAR-D6CZ-1G9600-D1XC	Two types of package are available
03-F 03/ W-0DIMA II	3.0  imes 2.5	FAR-D6GZ-1G9600-D1ZA	Two types of package are available
		()	Product of FUJITSU MEDIA DEVICES LIMITED)

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#### SAW Filter for Mobile Communication System

Correspondence system	Transmission/ Reception	Size (mm)	Part number	Remarks		
		2.0 × 1.6	FAR-F5EA-836M50-D27A	Unbalanced		
	Transmission	14,10	FAR-F5KA-836M50-D4DF Unbalanced			
		1.4 × 1.0	FAR-F5KB-836M50-B4EG	Balanced 200 ohm output		
			FAR-F5EA-881M50-D27B	Unbalanced		
CDMA/W-CDMA V,		2.0 × 1.6	FAR-F5EB-881M50-B2JJ	5 pins, Balanced 100 ohm output		
GSM850			FAR-F5EB-881M50-B28W	5 pins, Balanced 150 ohm output		
	Reception		FAR-F5KA-881M50-D4CH	Unbalanced		
		14,10	FAR-F5KB-881M50-B4ED	Balanced 100 ohm output		
		1.4 × 1.0	FAR-F5KB-881M50-B4EA	Balanced 150 ohm output		
			FAR-F5KB-881M50-B4EM	Balanced 150 ohm output		
	Transmission	2.0 × 1.6	FAR-F5EA-897M50-D27C	Unbalanced		
	Transmission	1.4 × 1.0	FAR-F5KA-897M50-D4DC	Unbalanced		
EGSM		20×16	FAR-F5EA-942M50-D27F	Unbalanced		
LOOM	Reception	2.0 × 1.0	FAR-F5EB-942M50-B28E	5 pins, Balanced 150 ohm output		
	Reception	14×10	FAR-F5KA-942M50-D4CJA	Unbalanced		
		1.4 × 1.0	FAR-F5KB-942M50-B4EB	Balanced 150 ohm output		
J-CDMA (32MHz)	Reception	1.4 × 1.0	FAR-F5KB-859M00-B4EE	Balanced 100 ohm output		
	_	20×16	FAR-F6EA-1G5754-L2AZ	Unbalanced		
		2.0 × 1.0	FAR-F6EB-1G5754-B2BS	5 pins, Balanced 100 ohm output		
GPS		1.4 × 1.0	FAR-F6KA-1G5754-L4AA	Unbalanced		
GFS	-		FAR-F6KA-1G5754-L4AJ	Uubalanced		
			FAR-F6KB-1G5754-B4GE	Balanced 100 ohm output, Low loss		
			FAR-F6KB-1G5754-B4GU	Balanced 100 ohm output, High Attenuation		
			FAR-F6EA-1G8425-D2ABA	Unbalanced		
		2.0 × 1.6	FAR-F6EB-1G8425-B2BG	5 pins, Balanced 150 ohm output		
DCS	Reception	14×10	FAR-F6EC-1G8425-B2CE	6 pins, Balanced 150 ohm output		
			FAR-F6KA-1G8425-D4CK	Unbalanced		
		1.4 ~ 1.0	FAR-F6KB-1G8425-B4GA	Balanced 150 ohm output		
	Transmission	2.0 × 1.6	FAR-F6EA-1G8800-L2AN	For Full Band		
	nanomiosion	1.4 × 1.0	FAR-F6KA-1G8800-L4AF	For Full Band		
			FAR-F6EA-1G9600-D2AC	Unbalanced		
		20×16	FAR-F6EB-1G9600-B2BK	5 pins, Balanced 100 ohm output		
GSM1900		2.0 ~ 1.0	FAR-F6EB-1G9600-B2BW	5 pins, Balanced 150 ohm output		
	Reception		FAR-F6EC-1G9600-B2CW	6 pins, Balanced 150 ohm output		
			FAR-F6KA-1G9600-D4CR	Unbalanced		
		1.4 × 1.0	FAR-F6KB-1G9600-B4GP	Balanced 100 ohm output		
			FAR-F6KB-1G9600-B4GB	Balanced 150 ohm output		
		2.0 × 1.6	FAR-F6EA-1G9500-D2AL	Unbalanced		
	Transmission		FAR-F6KA-1G9500-D4CD	Unbalanced		
	nanomiosion	1.4 × 1.0	FAR-F6KA-1G9500-D4DG	Unbalanced		
			FAR-F6KB-1G9500-B4GJ	Balanced 100 ohm input		
W-CDMA I		20×16	FAR-F6EB-2G1400-B2BN	5 pins, Balanced 100 ohm output		
		2.0 × 1.0	FAR-F6EC-2G1400-B2CP	6 pins, Balanced 200 ohm output		
	Reception		FAR-F6KA-2G1400-D4CG	Unbalanced		
		1.4 × 1.0	FAR-F6KB-2G1400-B4GC	Balanced 100 ohm output		
			FAR-F6KB-2G1400-B4GD	Balanced 200 ohm output		

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\*: Product of FUJITSU MEDIA DEVICES LIMITED

### SAW Dual Filter for Mobile Communication System

Correspondence system	Transmission/ Reception	Size (mm)	Part number	Remarks
		2.5 × 2.0	FAR-G6EE-1G8425-Y2PN	Balanced 150 ohm output, Opposite type of Filter position is available.
EGSM + DCS	Reception	2.0 × 1.6	FAR-G6KE-1G8425-Y4QG	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G6KG-1G8425-Y4SA	Balanced 150 ohm output, Opposite type of Filter position is available.
	Transmission	2.5  imes 2.0	FAR-G5ED-897M50-D2DE	Unbalanced
		2.5 × 2.0	FAR-G5EE-942M50-Y2PB	Balanced 150 ohm output, Opposite type of Filter position is available.
GSM850 + EGSM	Reception	2.0 × 1.6	FAR-G5KE-942M50-Y4QA	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G5KG-942M50-Y4SD	Balanced 150 ohm output, Opposite type of Filter position is available.
		2.5 × 2.0	FAR-G6EE-1G9600-Y2PR	Balanced 150 ohm output, Opposite type of Filter position is available.
DCS + GSM1900	Reception	2.0 × 1.6	FAR-G6KE-1G9600-Y4QB	Balanced 150 ohm output, Opposite type of Filter position is available.
		1.8 × 1.4	FAR-G6KG-1G9600-Y4SC	Balanced 150 ohm output, Opposite type of Filter position is available.
CDMA/W-CDMA V + US-PCS/W-CDMA II	Reception	2.0 × 1.6	FAR-G6KE-1G9600-Y4LY	Balanced 100 ohm output
J-CDMA (27 MHz + 6 MHz)	Transmission	1.8 × 1.4	FAR-G5KL-911M50-D4XA	Unbalanced, 1input/2output
	Transmission	1.8 × 1.4	FAR-G6KG-1G9500-Y4PG	Balanced 200 ohm input
	Reception	1.8 × 1.4	FAR-G6KG-2G1400-Y4SH	Balanced 200 ohm output

(Product of FUJITSU MEDIA DEVICES LIMITED)

# **Communication Control/Communication Network**



General purpose bus interface

### Communication Control

#### ISDN

Part number	Functions	Communication	Power supply	Package	
		standard	voltage (V)	QFP	
MB86434	AIU LSI for ISDN digital telephones, Internal CODEC, DTMF tones, service tone, and ringer tone	-	+5 ± 5%	64P	

Package: P - Plastic

#### **IP Packet Processing Engine**

Part number	Functions	Power supply	Package
T art number	T unctions	voltage (V)	LQFP
MB86977	Enable to process following functions with hardware. IP Packet Forwarding Packet Filtering NAT PPPoE and more. Supports QoS, DMZ, IPv6 and more. 10/100M MAC (Conforms to IEEE802.3)	$\begin{array}{c} 3.3\pm0.3\\ 1.8\pm0.15\end{array}$	208P

Package: P - Plastic

#### **High Speed IP sec Processing Engine**

Part number	Functions	Power supply	Package
Farthumber	T uncuons	voltage (V)	FBGA
MP96079	Inline Ipsec processing, DES / 3DES,AES,HMAC - SHA-1,HMAC-	$\textbf{3.3}\pm\textbf{0.3}$	337P
IVID60976	MD5,SA:64,IPv6,10 / 100M MAC	$\textbf{1.8} \pm \textbf{0.15}$	288P

Package: P - Plastic

### Communication Network

#### LAN

Part number	Functions	Communication	Power supply	Package	
	i unotiono	standard	voltage (V)	LQFP	
MB86967	10BASE-T Ethernet controller with PC card interface, ISA bus interface and General purpose bus interface	Conforms to IEEE 802.3	+5 ± 5%	100P	

Note: Ethernet is a registered trademark of XEROX Corporation of the USA.

Package: P - Plastic

### **Display Control Products**



### Display Control Products

#### Screen Display Control

OSDC (On-Screen Display Controller)

	Number Character - RGB Analog		ractor BGB A		RGB Analog Sync Po		Power		I	Packa	age					
Part number	Character generator	of character set	dot structure	Screen size	digital output	(video) output	signal generation	supply voltage (V)	SH- DIP	SOP	QFP	SSOP	FLGA			
MB90050	Internal ROM			35 characters × 16 lines	6bit (16 color selection in 64 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%	_		48P	_	_			
MB90096		512	24 × 32	32 characters				+5 ±10%	28P	28P	_	_	_			
MB90098A	Internal BOM	_			× 16 lines	4bit	4bit	4bit	Unavailable	Unavailable	+3.3	—	28P	—	—	—
MB90097					12 × 18	28 characters	28 12 × 18 characters × 12 lines	(16 colors)		onavallable	±0.3	—		—	20P	—
MB90099		1024	×	× 12 lines	× 12 lines	× 12 lines		× 12 lines				+2.4 to +3.6	_		_	20P
MB90092	External ROM	16384 (Max.)	24 × 32	24 characters × 12 lines	3bit (8 colors)	Composite Video and Y/C video	NTSC PAL	+5 ±10%		_	80P		_			

Package: P - Plastic

### **Video/Audio Products**



### Video/Audio Products

#### IF SAW Filter for Analog

IF SAW Filter for A	Analog	(Product of FUJITSU MEDIA DEVICES LIMITED)			
Applicable types	oplicable types System Video/Audio		Picuture carrier frequency (MHz)	Part number	
	Inter-Carrier (single)	Video	58.75	F081EPL	
	Split-Carrier (single)	Video	58.75	FAR-F4SA-58M750-A008	
NTSC N	Split-Carrier (single)	Video	58.75	FAR-F4SA-58M750-A019	
	Split-Carrier (single)	Audio	58.75	FAR-F4SA-54M250-B011	
	Split-Carrier (dual)	Video/Audio	58.75	FAR-G4SB-58M750-D018	
	Inter-Carrier (single)	Video	45.75	F072TPL-A	
NTSC M/N	Split-Carrier (single)	Video	45.75	FAR-F4SA-45M750-A024	
	Split-Carrier (single)	Audio	45.75	FAR-F4SA-41M250-B021	
	Split-Carrier (dual)	Video/Audio	45.75	FAR-G4SB-45M750-D025	
	Inter-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A041	
	Split-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A071	
PAL B/G/D/K/I	Split-Carrier (single)	Video	38.90	FAR-F4SA-38M900-A072	
	Split-Carrier (single)	Audio	38.00	F337MPL	
	Split-Carrier (single)	Audio	38.90	FAR-F4SA-40M400-B071	
	Split-Carrier (Switchable)	Video + Video	38.00	FAR-K4SD-38M000-F002	
NTSC M/N	Split-Carrier (Switchable)	Video + Video	38.00	FAR-K4SD-38M000-F011	
NTSO M/N	Split-Carrier (Switchable)	Video + Video	38.90	FAR-K4SD-38M900-F003	
	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G001	
PAL D/K/L B/G L/L'	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G002	
1 AL D/IVI, D/G, L/L	Split-Carrier (Switchable)	Audio + Audio	33.90/38.90	FAR-K4SD-40M400-G031	
	Split-Carrier (dual)	Audio + Audio	33.90/38.90	F817JPL	

#### **IF SAW Filter for Digital**

(Product of FUJITSU MEDIA DEVICES LIMITED)

Applicable types	Center frequency (MHz)	3 dB Bandwidth (MHz)	Part number			
DAB	38.912	1.50	SBF0402GPL			
	44.000	1.70	SBF0402JPL			
OOP	44.000	1.70	FAR-F4SE-44M000-A011			
OOB	44.000	2.60	FAR-F4SE-44M000-H0A6			
	44.000	4.00	FAR-F4SE-44M000-H0A3			
	36.000	8.10	FAR-F4SE-36M000-A005			
	36.125	6.10	FAR-F4SE-36M125-A001			
	36.125	7.00	SBF0407BPL			
	36.125	8.10	SBF0408KPL			
	43.750	6.00	FAR-F4SE-43M750-A006			
	43.750	6.00	FAR-F4SE-43M750-H0AB			
	44.000	5.35	FAR-F4SE-44M000-H0AG			
	44.000	5.37	FAR-F4SE-44M000-H0A4			
	44.000	5.42	FAR-F4SE-44M000-H0A8			
CATV/TV	44.000	5.49	FAR-F4SE-44M000-H0A1			
(US/Euro)	44.000	5.50	FAR-F4SE-44M000-H0AH			
	44.000	6.00	FAR-F4SE-44M000-H0A9			
	44.000	6.12	FAR-F4SE-44M000-H0A2			
	44.000	6.20	FAR-F4SE-44M000-H0AA			
	44.000	8.00	SBF0408LPL			
	47.250	6.20	FAR-F4SE-47M250-H0AC			
	36.000	6.4/7.4 (Switchable)	FAR-K4SH-36M000-L0E1			
	36.000	7.0/7.9 (Switchable)	SBSF03ABPL			
	36.125	6.0/7.9 (Switchable)	FAR-K4SH-36M125-F001			
	36.125	7.0/7.9 (Switchable)	SBSF03AAPL			
	57.000	5.30	FAR-F4SE-57M000-H0JC			
CATV/TV	57.000	5.40	FAR-F4SE-57M000-H0J9			
(Japan)	57.000	5.62	FAR-F4SE-57M000-H0J6			
	57.000	5.62	FAR-F4SE-57M000-H0J3			
	35.230	8.00	FAR-F4SE-35M230-A013			
TV tuner	36.125	6.90	FAR-F4SE-36M125-H0E8			
	36.125	7.60	FAR-F4SE-36M125-H0E5			
TV/STB	36.125	7.90	FAR-F4SE-36M125-H0E7			

#### **IF SAW Filter for Double ConversionI**

(Product of FUJITSU MEDIA DEVICES LIMITED)

Applicable types	Center frequency (MHz)	Bandwidth (MHz)	Part number		
1st IF	1220.000	8.00	FAR-F6CV-1G2200-C27A		

### **Video/Audio Products/Demodulator Products**

Ground Wave

Application Capacity Organization Part number Features EDID DTV/display 2K-bit 256 × 8 MB85RF402 For 4 DDC(I<sup>2</sup>C) ports memory for HDMI Application Part number Features Digital Small 48 pin package Satellite Demodulator High tolerance to spectrum distortion High and stability of MB86667 reception Blind Scan support Cable Small 48 pin package MB86668 High tolerance to spectrum distortion High and stability of reception

MB86A20

Support Japanese Terrestrial Digital TV and Digital Radio.

All memory such as time-interleave is implemented.

Input signal : 4MHz-IF or 57MHz-IF Output signal : serial or parallel TS

(Continued)

#### **EDID** memory

Part Number	Memory	Organization	Interface	Supply Voltage	Packages	
Fart Number	Memory	(W × b)	interface	(V)	TSSOP	
OMB85RF402	FRAM	256 × 8	For 4 DDC(I <sup>2</sup> C) ports	3.8 to 5.5	16P	

 $\bigcirc$  : New released.

Pakage : P - Plastic

### Demodulator Products

#### Satellite

Part number	Function	Power supply voltage (V)	Package
Part number	T unction	Power supply voltage (v)	QFP
MB86667	QPSK demodulator DVB-S and DSS support	1.65 to 1.95 3.0 to 3.6	48P

Package: P - Plastic

#### Cable

Part number	Eurotion	Power supply veltage (V)	Package
Farthumber	T unction	Power supply voltage (v)	QFP
MB86668	QAM demodulator DVB-C support	1.65 to 1.95 3.0 to 3.6	48P

Package: P - Plastic

#### **Ground Wave**

Part number	Eunction	Power supply voltage (V)	Package
Fait number	T unction	Power supply voltage (v)	FBGA
MB86A20	13 segment OFDM demodulator ISDB-T support	1.4 to 1.6 1.65 to 1.95 3.0 to 3.6	144P

Package: P - Plastic

# **Automotive Applications**



### Automotive Applications

#### **Graphics Display Controller**

Part number	Internal operation frequency	Rendering engine	Geometry engine	Max. graphics memory	Drawing	Display resolution (pixel)	No. of layer	Texture mapping (pixel)	Video capture input	Video scaling	Video output	Host interface	Power supply voltage (standard value)	Operation temp. range (°C)	Package			
MB86291A	100 MHz			2 MB SDRAM (built-in)			4	Max. 256 × 256	YUV	-	RGB analog/ digital		I/O: 3.3 V Internal: 2.5 V	-30 to +85	QFP- 208P			
MB86293				64 MB SDRAM (external)	2D/3D	Max. 1024 × 768			-	-	RGB digital	32 bit parallel			QFP- 256P			
MB86294	133 MHz	MHz Built-in MHz	Built-in				6 (included 1 alpha plane)		YUV	Down	RGB analog/		I/O: 3.3 V Internal: 1.8 V		QFP- 256P BGA- 256P			
MB86296			Built-in	Built-in	Built-in						Max, 4096	YUV/ RGB	Up/ Down	uigitai	PCI 33 MHz	<u>.</u>		BGA- 256P
MB86297A	266 MHz										128 MB DDR- SDRAM (external)		Max. 1280 × 1024 8 (p 4 al plan	8 (plus 4 alpha plane)	× 4096	YUV × 2/ RGB + YUV	Up/ Down	RGB digital × 2
MB86276	133 MHz	-	64 MB SDRAM (external)	2D	Max. 1280 × 768	6 (included 1 alpha plane)		YUV/ RGB	Up/ Down	RGB digital	32/16 bit parallel Address/ data bus multiplex	I/O: 3.3 V Internal: 1.8 V		PBGA- 320P				

Packages: P - Plastic



(Continued)

#### AC/DC Converters

		Power supply	No of	Operating oscillator	Refere	ence voltage	Package
Part number	Function	voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	SOP
MB3759	PWM-type controllers for AC/DC converters	+7 to +32	1	300	5	5.0	16P
MB3769A		+12 to +18		700	5	2.0	16P

Packages: P - Plastic

#### General Purpose DC/DC Converters

Part number	Function	Power supply	No. of	Operating oscillator frequency	Referen	ice voltage	Solutions	I	Packa	ge
		voltage (V)	Channels	(kHz) (Max.)	(V) (Typ.)	Precision (%)		SOP	SSOP	TSSOP
MB3789		+3.0 to +18		200	2.5	4.0	Up conversion	-	16P	-
MB3817	PWM-type	+2.5 to +18	1	500	1.5	2.0	Up conversion Down conversion Invert		16P	-
MB3885	DC converters	+5.5 to +18	I		1.25	1.0	Down conversion	-	20P	-
MB3800		+1.8 to +15		1000	0.5	4.0	Up conversion	8P	8P	-
OMB39A135		+4.5 to +25		1000	0.7	1.0	Down conversion	-	-	24P
MB3775		+3.6 to +18			1.28	1.5	Up conversion	16P	16P	-
MB3778		+3.0 10 +10			2.46	2.0	Invert	16P	16P	-
MB3882		+5.5 to +18	500	1.25			-	24P	-	
MB3889				2	1.00	1.23			-	30P
MB39A106	controllers for DC/	-6 5 to -19	2		1.23				-	30P
MB39A116A	DC converters	+0.5 10 +16			1.00	1.0	Down conversion	-	-	30P
OMB39A136		+4.5 to +25		1000	0.7				-	16P
MB39A104		+7 to +19		1500	1.24			-	24P	-
MB39C011 MB39C011A		+4.5 to +17		2000	1.0			I	_	16P
MB3782	PWM-type controllers for DC/	+3.6 to +18	3	500	2.5	2.0	Up conversion Down conversion Invert	20P	_	-
MB39A112	DC converters	+7 to +25		2600	(1.0/ 1.23)	1.0	Down conversion	_	-	20P

○: New product

Packages: P - Plastic



(Continued) (Continued)

#### DC/DC converters with switching FET

Part number	Function	Power	No. of	Operating oscillator	Referer	ice voltage	Output current	Switch ON res	ing FET istance	Colutions	Pack	age
		voltage (V)	channels	(kHz) (Max.)	(V) (Typ.)	Precision (%)	DC/DC (mA) (Max)	Pch MOS (W) (Typ)	Nch MOS (W) (Typ)	Solutions	QFN	SON
MB39C014	39C014 PWM type DC/DC 39C015 converters	+2 5 to +5 5	1	2000/3200 (Fix)	1.20	2.0	800	03	0.2	Down	1	10P
MB39C015		+2.3 10 +3.3	2	2000 (Fix)	1.30	2.0	000	0.5	0.2	conversion	24P	-

Packages: P - Plastic

#### DC/DC converters with switching FET + LDO

Part number	Function For	Power supply	No. of	Operating oscillator frequency (kHz)	Reference voltage (V) (Typ.)	Output voltage (V) (Typ.)	Precision (%)	Output current (mA) (Max.)	Switching FET ON resistance		I/O potential	Solutions -	Package	
		voltage (V)	channels						Pch MOS (Ω) (Typ)	Nch MOS (Ω) (Typ)	(mV) (Typ.)	Solutions	SON	
⊚MB39C022G	DC/DC converter	+2.5 to	1	2000 (Fix)	0.3	Ì	±2.5	600	0.3	0.2	-	Down		
	©MB39C022G	LDO	+2.5 10 +5.5	+2.5 10 +5.5	1	_	_	3.3 (Fix)	±2.5	300	_	_	200 (lo = -300mA)	conversion
©: Now planning Packages: P - Plastic														

©: Now planning

#### DC/DC converters for RF Power Amp.

Part number	Function	Power	No. of channels	Operating oscillator	Reference voltage		Output current		Switching FET ON resistance			Ochstiene	Package
		voltage (V)		(kHz) (Max.)	(V) (Typ.)	Precisi on (%)	DC/DC (mA) (Max)	Bypass FET (mA) (Max)	Pch MOS (Ω) (Typ)	Nch MOS (Ω) (Typ)	Bypass FET (Ω) (Typ)	Solutions	QFN
MB39C018	PWM type DC/DC converters Built in Bypass FET	+2.5 to +5.5	1	2000 (Fix)	1.24	1.5	800	1000	0.3	0.2	0.08	Down conversion	24P

Packages: P - Plastic

#### DSC/Camcorder DC/DC Converters

Part number	Function	Power	No. of	Operating oscillator	Refe vo	erence Itage	Solutions	Drive	Package		
	Tunction	voltage (V)	channels	frequency (kHz) (Max.)	(V) (Typ.)	Precision (%)	Controlls	circuit	LQFP	BCC	TSSOP
MB3785A		+4.5 to +18		1000	2.5		Down conversion	PNP :4	48P	_	—
MB39A102		+2.5 to +11		1500			Up conversion Down conversion Up/Down conversion	Pch : 3, Nch : 1		32P	30P
MB39A103		+1.7 to +11 +2.5 to +11	4	1500				Pch : 1, Nch : 3	—	32P	30P
MB39A110					2.0			Pch : 3, Nch : 1	—	_	38P
MB39A108	PWM-type	17 to 11	5	2000				Pch : 3, Nch : 2	—	40P	38P
MB39A115	for DC/DC	+1.7 10 +11	5			1.0		Pch : 4, Nch : 1	—	40P	38P
MB3825A	conveniers	+2.5 to +12		800	1.5		Down conversion	PNP:6	64P**	_	
MB3883		+1.7 to +9	6	1000	2.5		Up conversion Down conversion Up/Down conversion	Pch : 2, Nch : 4	48P	48P	_
MB39A123		+1.7 to +11		2000	2.0		Up conversion Down conversion Up/Down conversion Invert	Pch : 4, Nch : 2	48P	48P	_
MB3881	<u> </u>	+1.8 to +13	8	800	2.5	<u> </u>	Down conversion Up/Down conversion	Pch : 7, Nch : 1	64P*	_	_

\*: 0.4 mm pitch


### DSC/Camcorder DC/DC Converters

Part number	Part number Function Power supply voltage (V)		No. of	Operating oscillator	Reference voltage		Solutions	Drive circuit	Package
			channels frequency (kHz) (Max.)		(V) (Typ.)	Precision (%)	Controlla	Brive circuit	FBGA
MB39C306	PWM-type	+2.5 to +6	7	1500	2.4	1.0	Up conversion Down conversion	All channel with	103P
MB39C309 converters +2		+2.5 to +5.5	7 (DC/DC) 2 (LDO	1500	2.4	1.0	Up/Down conversion Invert	FETs	82P

Packages: P - Plastic

#### **Rechargeable Battery (Charge control)**

		Power	• • •				Operating	I	Ρ	Package		
Part number	Function	supply	Output voltage	Pre	cision (%)	Number	oscillator	Solutions				
		voltage (V)	(V)	Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	LQFP	QFN	
MB3876		+7 to +25	16.8	+0.8	+1.0	1			24P	-	_	
MB3877		Ŧ7 10 Ŧ25	10.0	±0.0	±1.0	-			24P	-	-	
MB3879			12.6/16.8	±0.8	±1.0					48P		
WIB0075			12.3/16.4	±0.9	±0.9 ±1.1	_				-01		
MB39A114	Charge control	+8 to +25	12 6/16 8	±0.5	±0.74 *	3/4	500	Down	24P	-	-	
MB39A126	DC/DC converters		12.0, 10.0	±0.6	±0.80 *		500	conversion	24P	_	28P	
MB3875		17 to 125	12.6	±0 8	+1.0	2			24P	-	-	
MB3874		+7 10 +25	12.0	<u>1</u> 0.0	±1.0	5			24P	-	_	
MB3832A		+3.6 to +18	Any voltage level	±0.5	±1.0*	1 to 3			20P	_	_	

\* : Ta = -10 to +85 °C

Package: P-plastic

### **Power Management Applications**



(Continued)

#### **Rechargeable Battery (Charge control)**

		Power					Operating	Solutions	Pa	Package			
Part number	Function	supply	Output	Pre	cision (%)	Number	oscillator frequency						
		voltage (V)	voltage (V)	Ta = +25 °C	Ta = -30 to +85 °C	of cells	(kHz) (Max.)		SSOP	TSSOP	QFN		
MB3878		+7 to +25	4.2 \//coll	±0.8	±1.0				24P	_	-		
MB3887			4.2 V/Cell	+0.6 -0.4			500		24P	-	-		
MB3888				Any voltage level ±0.74 * 1 to 4	1 to 4	1 to 4		20P	_	-			
MB39A113	Charge								24P	-	-		
MB39A118	control		4.2 V/cell	4.2 V/cell	4.2 V/cell	10.5			1000	Down	-	-	28P
MB39A119	converters	+8 to +25		±0.5	±0.74 *	*	1000	conversion	-	-	28P		
MB39A125							500		24P	-	28P		
MB39A129			4.145V/Cell, 3.75V/Cell, Any voltage level		±0.7 *	2 to 4	2000		24P	_	_		
⊖MB39A134			4.2V/Cell, 4.1V/Cell, Any voltage level	±0.5	±0.7 *	2 to 4	2000		_	24P	_		
* : Ta = -10 to +8	Ta = -10 to +85 °C Package: P-plastic												

\* : Ta = -10 to +85 °C

○: New product

DC/DC converters for Ultra Mobile PC

		Input	Number of channels	Oscillator frequencies (kHz)		Out		Package		
Part number	Function	voltage (V)			Pin name	Preset Output Voltage (V)	FET	Drive or Output current (A) (Max)	Solutions	PBGA
	DC/DC				CH1	5	Extornal	2		
				700	CH2	3.3	LAtemai	4.5		
	converters	+5.5 to			CH3	1.8/1.5		2.7	Down conversion	2080
OMB39C308	Platform	+12.6	0	(Fix)	CH4	0.9/0.75	Integrated	1.5		2005
	VR	VR			CH5	1.5	- Integrated	2.5		
					CH6	1.05		3.5		

LPIA=Low Power Intel Architecture®

⊖: New product

Package: P-plastic

### **Power Management Applications**

(Continued)



#### **Voltage Detectors**

Part number	Eunction	Power supply voltage	Reference voltage	Package
Faithumber	i unction	(V)	(V) (Typ.)	SOP
MB3761	Voltage detector	+2.5 to +40	1.2	8P

Package: P - Plastic

#### **Supply Voltage Monitoring Applications**

		Power supply	<b>D</b>	Reset certified	Package	
Part number	Function	voltage (V)	Detection voltage (V)	voltage (V) (Typ.)	SOP	SSOP
MB3771	Supply voltage monitoring applications	+3.5 to +18	Any voltage level in		8P	-
MB3773	Supply voltage monitoring applications with watchdog timer	+3.5 to +16	addition to 4.2 V		8P	-
MB3793-27A *1		+4 (Max )	2.7±0.07		8P	8P
MB3793-28A *1		++ (Wax.)	2.8±0.07		8P	8P
MB3793-30A *1			3.0±0.07	0.8	8P	8P
MB3793-34A *1	Supply voltage monitoring applications		3.4±0.08		8P	(8P) <sup>*2</sup>
MB3793-37A *1		+6 (Max.)	3.7±0.1		8P	(8P) <sup>*2</sup>
MB3793-42 *1	]		4.2±0.1		8P	(8P) <sup>*2</sup>
MB3793-45 *1			4.5±0.1		8P	8P

\*1:Detection voltages of the MB3793 series are available in the range from 2.4 V to 4.9 V in 0.1 V increments. Package: P - Plastic Consult with supplier.

\*2:() option

#### **Switching Applications**

Part number	Eurotion	Power supply	Number of	On-resistance	Drive current	Package	
Farthumber	Tunction	voltage (V) (Max.)	channels	<b>(</b> Ω <b>)</b>	(A) (Max.)	SOP	SSOP
MB3841			1	0.045	2.0	8P	-
MB3842	Power management switch	5.5	2	0.1	0.6		20P
MB3845			2	0.1	0.0	_	201

Package: P - Plastic

#### LCD Panel

	DC/DC Block							Gamı gene	<b>)</b>	Package	
Part number	Function	Power supply voltage (V)	Number of channels	Reference voltage (V)	Precision (%)	Oscillation frequency (kHz)(Max)	Solution	Gamma voltage number of channel	VCOM voltage number of channel	DAC (bit)	BCC
OMB39C307A	DC/DC + Gamma voltage generator	+4.5 to +17	6	1 1.25	± 1.0	600	Step down 3ch Step up 2ch Invert 1ch	20	1	10	92P *
: New product									Pack	age: F	· - Plastic

\*: With exposed pad

#### LCD Panel

Part number	Function	Power supply voltage (V)	Number of channels	Reference voltage (V)	Precision	Oscillation frequency (kHz)	Solution	Package TSSOP	
	2ch. DC/DC + 2ch. charge pump	+8 to +14	4	1.213	± 1.0%		Step down	28P *	
@MR20C212				1.146	± 1.0%	500/750	Step up		
©MB39C313				0	± 36mV	500/750	Invert charge pump		
				1.213	± 1.0%		Step up charge pump		

©: Now planning

\*: With exposed pad

Package: P - Plastic

### **Motor Drivers/Sensor Conditioner**



### Motor Drivers

Part number	Function	Number of Channels	Output current	Power supply voltage	Package
Faithumber	Tunction	Number of Chamleis	(mA)	(V)	SOP
MB3763	Reversible motor drivers	1	300	+4 to +18	8P
MB3863		2	500	+4 to +36	20P

Package: P - Plastic

### Sensor Conditioner

		Temperature	Numberof		Power		Pac	kage
Part number	Function	compensation method	detection circuits	Gain	supply voltage (V)	Others	всс	SSOP
MB42M101	For bridge resistance Detection circuit	Look-up table	3	240 to 2860 V/V	3.0 to 5.5	Digital compensation Constant current drive Built-in memory 1280 bits	32P	_
MB42M102	For bridge resistance Detection circuit	Continuous linear apporoximation	3	240 to 2860 V/V	4.5 to 5.5	Digital compensation Constant current drive Built-in memory 1280 bits Diagnosis circuit	40P	_
MB42M104	For bridge resistance Detection circuit	Continuous linear apporoximation	3	30 to 2005 V/V	4.5 to 5.5	Digital compensation Constant voltage drive Built-in memory 1280 bits Diagnosis circuit	40P	_
⊚MB42M121	For bridge resistance Detection circuit	Continuous linear apporoximation	1	20 to 500 V/V	2.7 to 3.6	Digital compensation Constant voltage drive Built-in memory 1280 bits Diagnosis circuit	_	20P
⊚MB42M131	For bridge resistance Detection circuit	Continuous linear apporoximation	3	252 to 531 V/V	2.7 to 3.6	Digital compensation Constant voltage drive	20P	-

⊚: Now planning

Package: P - Plastic

## **Fingerprint Sensor**



# AUGE

### Fingerprint Sensor

Part number	Resolution	Sensor area	Sensor array	Power supply	Interface	Others	Package	
	(dpi)	(mm)	(pixel)	(V)	Interface		TSOP	FBGA
MBF200	500	12.8 × 15.0	256 × 300	3.3 to 5.0	8bit MPU SPI USB 1.1	-	80P	-
MBF310		10.9 × 0.5	218 × 8	2.7 to 3.3	8bit MPU SPI	FIFO	-	43P

Package: P - Plastic

### Smart Card/RFID (FerVID family™) /Secure



# Smart Card/RFID (FerVID family™) /Secure

### Smart Card

Part number	Interface	CPU (bit)	FRAM (byte)	ROM (byte)	SRAM (byte)	Code Type	Shipment form
MB89R076	ISO14443 TypeB	8	4K	32K	512	DES	An exclusive package
MB94R215B	ISO14443 TypeB, ISO7816	32	32K	128K	8K	DES/RSA	An exclusive package

### RFID (FerVID family™)

Part number	Frequency band	Interface	Transmission speed (Reader/Writer -> LSI)	Transmission speed (LSI -> Reader/Writer)	FRAM (byte)	Shipment form
MB89R111		ISO14443 TypeB	106kbps, 212kbps	106kbps, 212kbps	2K	Wafer
MB89R118	13.56MHz	ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	2K	Wafer (With a golden Bump)
MB89R119		ISO15693	26.48kbps (52.97kbps)	26.48kbps (52.97kbps)	256	Wafer (With a golden Bump)
OMB97R8010		ISO18000-6 TypeB	10kbps, 40kbps	10kbps, 40kbps	1K	Wafer (With a golden Bump)
OMB97R8020		ISO18000-6 TypeB	10kbps, 40kbps	10kbps, 40kbps	256	Wafer (With a golden Bump)

 $\bigcirc$ : New product

### Secure

Part number	CPU	FRAM	ROM	SRAM	Code Type	Power supply voltage	Package
i art number	(bit)	(byte)	(byte)	byte) (byte) Code Type	oode Type	(V)	QFP
MB89R907A	8	4K	32K	1K	Elliptic Curve Cryptography (ECC)	+5 ± 5%	48P

Package: P - Plastic

### **General-Purpose Converter**



### General-Purpose Converter

#### A/D Converter

Part number	Function	Conversion	Conversion time	time time cror (%)		Package				
		method	(µs/ch) (Max.)	(Max.)	voltage (V)	DIP	SOP	SSOP	QFP	SH-DIP
MB88111	24-ch 10-bit A/D converter	Successive	50	±1 LSB	+3.5 to +5.5	Ι	_	Ι	44P	48P
MB88101A	4-ch 12-bit A/D converter	approximation	16 (at 5 V±10%)	-4.0 to +2.0 LSB	+3.3 to +5.5	16P	16P	16P	I	_

Packages: P - Plastic

#### D/A Converter for Digital Tuning Applications

Part number	Function	Settling time	Power	Non- linearity	Power supply		Pac	kage	
i un number	i unotori	(μs) (Max.)	(mW) (Typ.)	error (LSB)	(V)	DIP	SOP	SSOP	QFP
MB88346B	12-ch 8-bit D/A converter (internal operational amplifier)	20	14		+5±10%	20P	20P	20P	I
MB88346L	12-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	300	5		+2.7 to +3.6	20P	20P	20P	_
MB88347	8-ch 8-bit D/A converter (internal operational amplifier)	100	9		+5±10%	16P	16P	16P	-
MB88347L	8-ch 8-bit D/A converter (internal operational amplifier, low voltage operation)	200	4.2	±1.5	+2.7 to +3.6	16P	16P	16P	_
MB88345	24-ch 8-bit D/A converter (internal operational amplifier)	100	27			_	_	_	32P
MB88141 *	12-ch 8-bit D/A converter		15		+5±10%	24P	24P	24P	-
MB88141A <sup>*</sup>	internal operational amplifier) 100				2 11	2 11	2 11	-	
MB88146A	2-ch 8-bit D/A converter /O expander, internal perational amplifier)			Digital:+2.7 to +5.5 Analog:+5±10%	24P	_	24P	1	

Package: P - Plastic

\* "Purchase of Fujitsu Microelectronics I<sup>2</sup>C components conveys a license under the Philips I<sup>2</sup>C Patent Rights to use these components in an I<sup>2</sup>C system, provided that the system conforms to the I<sup>2</sup>C Standard Specification as defined by Philips."

### **Spread Spectrum Clock Generator**



### Spread Spectrum Clock Generator

Port number	Eurotion	Power	Input	Efficiency	Output	Modulation	Modulation	Other	Package			
Part number	Function	voltage	(MHz)	multiply	(MHz)	Туре	sensitivity	Other	SOP			
MB88151A-100				× 1	16.6 to 33.4			PD function disable				
MB88151A-101					10.0 10 00.4			PD function enable				
MB88151A-200				~ 2	33 2 to 66 8			PD function disable				
MB88151A-201			16 6 to 22 4	~ 2	55.2 10 00.8		-1.0%, -3.0% (down)	PD function enable				
MB88151A-400			10.0 10 33.4	~ 4	66.4 to	Down or	±0.5%, ±1.5% (center)	PD function disable	00			
MB88151A-401				× 4	133.6	(selection)	(no modulation setting is no PD	PD function enable	OF			
MB88151A-500				v 1/0	9 2 to 16 7		product)	PD function disable				
MB88151A-501				× 1/2	0.3 10 10.7			PD function enable				
MB88151A-800			9 2 to 16 7		66.4 to			PD function disable				
MB88151A-801	EMI noise reduction	3.3	0.3 10 10.7	×o	133.6			PD function enable				
MB88152A-100	(SSCG)	± 0.3	16.6 to 40 33 to 67		16.6 to 40 33 to 67	Down	-1.0%, -3.0%					
MB88152A-110			40 to 80 66 to 134		40 to 80 66 to 134	Center	±0.5%, ±1.5%					
MB88152A-101			16.6 to 40	√ 1	16.6 to 40	Down	-1.0%, -3.0% no modulation	_	۹D			
MB88152A-111			33 to 67	~ 1	33 to 67	Center	$\pm 0.5\%, \pm 1.5\%$ no modulation	-	OF			
MB88152A-102			40 to 80		40 to 80	Down	-1.0%, -3.0% no modulation					
MB88152A-112			66 to 134		66 to 134	Center	$\pm 0.5\%, \pm 1.5\%$ no modulation					
MB88153A-100			16.6 to 40		16.6 to 40	Down	-1.0%, no modulation					
MB88153A-101			66 to 134	× 1	66 to 134	Domi	-3.0%, no modulation	PD function	8P			
MB88153A-110			33 to 67		33 to 67	Center	±0.5%, no modulation	enable				
MB88153A-111			40 10 00		40 10 00		±1.5%, no modulation					
MB88154A-102			33 to 67		33 to 67	67 Down -1.0%, -2.0%,						
MB88154A-103			16.6 to 40	× 1	16.6 to 40	.0	40	10	no modulation	no modulation	REF output	8P
MB88154A-112			33 to 67		33 to 67	7 Center	Center ±0.5%, ±1.0%,	enable	-			
MB88154A-113			16.6 to 40		16.6 to 40		±1.5%, no modulation					

Package: P - Plastic (Continued) (Continued)



arbitrarily set by the mask option.

(Continued)

		Power	Input	Efficiency	Output				Pack	age
Part number	Function	supply voltage (V)	frequency (MHz)	of multiply	frequency (MHz)	Modulation Type	Modulation sensitivity	Other	TSSOP	BCC
MB88155-100			12.5 to 25		12.5 to 25		-1.0%, -2.0%	PD function		
MB88155-101			25 to 50		25 to 50	Down	no modulation	disable		
MB88155-102			12.5 to 25		12.5 to 25	Down	-1.0% -2.0%	PD function		
MB88155-103			25 to 50	× 1	25 to 50		1.070, 2.070	enable		
MB88155-110			12.5 to 25		12.5 to 25	-	±0.5%, ±1.0%	PD function		
MB88155-111			25 to 50		25 to 50	Center	no modulation	disable		
MB88155-112	-		12.5 to 25		12.5 to 25	-	±0.5%, ±1.0%	PD function		
MB88155-113	-		25 to 50		25 to 50			enable	8P	-
MB88155-400						Down	-1.0%, -2.0% no modulation	function disable		
MB88155-402			12 5 to 20	× 4	2 4 50 to 80		-1.0%, -2.0%	PD function enable		
MB88155-410		3.3 + 0.3	12.0 10 20		SU IO 80		$\pm 0.5\%, \pm 1.0\%$ no modulation	PD function disable		
MB88155-412		10.0			Center		±0.5%, ±1.0%	PD function enable		
MB88156-000			20 to 28 ( × 1)	× 1, × 2,	20 to 28 ( × 1)		-1.0%, -2.0%, ±0.5%,	REFoutput enable		100
MB88156-001	EMIncipa		14 to 40 ( × 2)	(selection)	28 to 80 ( × 2)	Down/ Center	modulation	REFoutput disable		IOF
MB88161	reduction PLL (SSCG)		$\begin{array}{c} 12 \text{ to } 28 \\ (\times 1) \\ 20 \text{ to } 42 \\ (\times 4) \end{array}$	$\times$ 1, $\times$ 4, (selection)	12 to 28 ( × 1) 80 to 168 ( × 4)	(selection)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P
MB88162			$\begin{array}{c} 12 \text{ to } 28 \\ (\times 1) \\ 20 \text{ to } 42 \\ (\times 4) \end{array}$	$\times$ 1, $\times$ 4, (selectable)	12 to 28 ( × 1) 80 to 168 ( × 4)	Down/ Center (selectable)	-1.0%, -2.0%, -4.0%, ±0.5%, ±1.0%, ±2.0%, no modulation	PD function enable	-	18P
⊚ MB88163			12.5 to 26	v 1	12.5 to 26		$\pm 0.5\%,$ no modulation	-	-	6P
© MB88163-100					20 to 42					
⊚ MB88163-200		1.8 ± 0.15	20 to 42	× 2	40 to 84	Center	±0.25%, ±0.5%,	OE	00	
⊚ MB88163-400				× 4	80 to 168		±1.0%, no modulation	enable	ð٢	-
© MB88163-500			12.5 to 26	× 1	12.5 to 26					
MB88181		3.3 ± 0.3	16 to 32	× 1/2 or more *	8 to 166	Center	±0.5%, ±1.0%, ±1.5%, ±2.0%, no modulation	PD function enable, Clock output 8(Max.)	20P	-

\*: The efficiency of multiply and the output mode can be arbitrarily set by the mask option.

©: Now planning

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Package: P - Plastic

# Spread Spectrum Clock Generator

#### SSCG Simple Evaluation Board

	Part number	Remarks						
	MB88151AEB01-100	MB88151A-100 mounted						
	MB88151AEB01-101	MB88151A-101 mounted						
	MB88151AEB01-200	MB88151A-200 mounted						
	MB88151AEB01-201	MB88151A-201 mounted						
	MB88151AEB01-400	MB88151A-400 mounted						
NID00151A	MB88151AEB01-401	MB88151A-401 mounted						
	MB88151AEB01-500	MB88151A-500 mounted						
	MB88151AEB01-501	MB88151A-501 mounted						
	MB88151AEB01-800	MB88151A-800 mounted						
	MB88151AEB01-801	MB88151A-801 mounted						
	MB88152AEB01-100	MB88152A-100 mounted						
	MB88152AEB01-110	MB88152A-110 mounted						
MDOO150A	MB88152AEB01-101	MB88152A-101 mounted						
WID00152A	MB88152AEB01-111	MB88152A-111 mounted						
	MB88152AEB01-102	MB88152A-102 mounted						
	MB88152AEB01-112	MB88152A-112 mounted						
	MB88153AEB01-100	MB88153A-100 mounted						
MD00150A	MB88153AEB01-101	MB88153A-101 mounted						
NID66153A	MB88153AEB01-110	MB88153A-110 mounted						
	MB88153AEB01-111	MB88153A-111 mounted						
	MB88154AEB01-102	MB88154A-102 mounted						
	MB88154AEB01-103	MB88154A-103 mounted	An oscillation vibrator. oscillation					
WD00104A	MB88154AEB01-112	MB88154A-112 mounted	stable capacity, and a power supply					
	MB88154AEB01-113	MB88154A-113 mounted	line are required.					
	MB88155EB01-100	MB88155-100 mounted						
	MB88155EB01-101	MB88155-101 mounted						
	MB88155EB01-102	MB88155-102 mounted						
	MB88155EB01-103	MB88155-103 mounted						
	MB88155EB01-110	MB88155-110 mounted						
MB99155	MB88155EB01-111	MB88155-111 mounted						
WID00133	MB88155EB01-112	MB88155-112 mounted						
	MB88155EB01-113	MB88155-113 mounted						
	MB88155EB01-400	MB88155-400 mounted						
	MB88155EB01-402	MB88155-402 mounted						
	MB88155EB01-410	MB88155-410 mounted						
	MB88155EB01-412	MB88155-412 mounted						
MB88156	MB88156EB01-BC16-000	MB88156-000 mounted						
MB00100	MB88156EB01-BC16-001	MB88156-001 mounted						
MB88161	MB88161EB01	MB88161 mounted						
MB88162	MB88162EB01	MB88162 mounted						
	©MB88163EB01	MB88163 mounted						
	©MB88163EB01	MB88163-100 mounted						
MB88163	©MB88163-200EB02	MB88163-200 mounted	1					
	©MB88163-400EB02	MB88163-400 mounted						
	©MB88163-500EB02	MB88163-500 mounted						

○: Now planning



Memory Product Line-up

\* : ASM = Application Specific Memory

FCRAM is a trademark of Fujitsu Microelectronics Limited.



MirrorBit is a trademark of Spansion Inc. ORNAND is a trademark of Spansion Inc.

# FCRAM<sup>™</sup> (Fast Cycle RAM) (1)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

### ■ Mobile FCRAM<sup>TM</sup> (Fast Cycle RAM)

• 16M-bit Async. SRAM Type FCRAM

Organization (W × b)		Initial Page M		e Mode Burst Made F		Supply	Supply		
	Part Number	Access Time Max. (ns)	Access Time Max. (ns)	Frequency Max. (MHz)	Access Time Max. (ns)	Operating (mA)	Standby (µA)	Power Down (μΑ)	Voltage (V)
1M v 16	MB82D01181E-60L *1	60	N/A	N/A	N/A	20	100 * <sup>3</sup>	10	2.3 to 3.5
TIVE X TO	MB82DS01181E-70L *2	70	N/A	N/A	N/A	20	100	10	1.7 to 1.95

\*1: Shipping form: Chip, wafer, 48-pin FBGA package (SRAM compatible pinout)

\*2: Shipping form: Chip, wafer

Package support for mass production is T.B.D.

\*3: At V<sub>DD</sub> ≤ 3.1V

#### • 32M-bit Async. /Sync. SRAM Type FCRAM

Initial Supply Current Max. Page Mode Burst Clock Access Burst Mode Organization Supply Access Access Power Time Part Number Frequency Operating Standby (W × b) Time Time Voltage (V) Max. (MHz) Down Max. (mA) (μA) Max. (ns) Max. (ns) (μ**Α**) (ns) \*4 MB82DP02183E-65L 65 20 N/A N/A 30 120 10 2.6 to 3.1 8 \*<sup>5</sup>  $2M \times 16$ 70 20 83 30 120 10 1.7 to 1.95 MB82DBS02163E-70L 70 N/A 104 7 \*6 30 120 10 1.7 to 1.95 MB82DBS02154E-70L \*1: Compliant with COSMORAM spec

\*2: MB82DP02183E : with Page mode

MB82DBS02163E : with SDR Burst mode & Page mode

MB82DBS02154E : with SDR Burst mode & Multiplexed Address and Data Bus

\*3: Shipping form: Chip, wafer, 71-pin FBGA package

- \*4: At asynchronous operation
- \*5: At RL = 5, 6
- \*6: At RL = 7

#### • 64M-bit Async. /Sync. SRAM Type FCRAM

\*1, \*2, \*3

\*1, \*2, \*3

		Initial	Page Mode	Burst Made	Burst Clock	Supply	Supply		
Organization (W × b)	Part Number	Access Time Max. (ns) * <sup>4</sup>	Access Time Max. (ns)	Frequency Max. (MHz)	Access Time Max. (ns)	Operating (mA)	Standby (μΑ)	Power Down (μΑ)	Voltage (V)
	MB82DP04184E-65L	65	20	N/A	N/A	40	200	10	2.6 to 3.1
4M × 16	MB82DBS04164E-70L	70	20	104	7 * <sup>5</sup>	40	200	10	1.7 to 1.95
	MB82DBS04154E-70L	70	N/A	104	7 * <sup>5</sup>	40	200	10	1.7 to 1.95

\*1: Compliant with COSMORAM spec

\*2: MB82DP04184E : with Page mode

MB82DBS04164E : with SDR Burst mode & Page mode

MB82DBS04154E : with SDR Burst mode & Multiplexed Address and Data Bus \*3: Shipping form: Chip, wafer

Package (71-pin FBGA) support for mass production is T.B.D.

\*4: At asynchronous operation

\*5: At RL = 6, 7

# FCRAM<sup>™</sup> (Fast Cycle RAM) (2)



(Continued)

FCRAM is a trademark of Fujitsu Microelectronics Limited.

#### • 128M-bit Async. /Sync. SRAM Type FCRAM

		Initial	Page Mode	Rurst Mode	Burst Clock	Supply	Supply		
Organization (W × b)	Part Number	Access Time Max. (ns) * <sup>3</sup>	Access Time Max. (ns)	Frequency Max. (MHz)	Access Time Max. (ns)	Operating (mA)	Standby (µA)	Power Down (μΑ)	Voltage (V)
8M × 16	MB82DBS08164C-70L	70	N/A	104	6 * <sup>4</sup>	40	300	10	1.7 to 1.95
01VI × 10	O MB82DBS08164D-70L	70	N/A	104	6 * <sup>4</sup>	35 * <sup>5</sup>	200	10	1.7 to 1.95

O: New Product

\*1: Compliant with COSMORAM spec, with SDR Burst mode

\*2: Shipping form: Chip, wafer

Package support for mass production is T.B.D.

\*3: At asynchronous operation

\*4: At RL = 6, 7

\*5: T<sub>A</sub> <u>≤</u> +40 °C

#### • 256M-bit Async. /Sync. SRAM Type FCRAM

		Initial	Page Mode	Burst Mode	Burst Clock	Supply	Supply		
Organization (W × b)	Part Number	Access Time Max. (ns) * <sup>3</sup>	Access Time Max. (ns)	Frequency Max. (MHz)	Access Time Max. (ns)	Operating (mA)	Standby (μΑ)	Power Down (μΑ)	Voltage (V)
16M × 16	MB82DBS16164A-80L	80	N/A	100	7 *4	40	250 * <sup>5</sup>	10	1.7 to 1.95
$8M \times 32$	MB82DBS08314A-80L	80	N/A	100	7 *4	40	250 * <sup>5</sup>	10	1.7 to 1.95

\*1: Compliant with COSMORAM spec, with SDR Burst mode

\*2: Shipping form: Chip, wafer

Package(115-pin FBGA) support for mass production is T.B.D.

- \*3: At asynchronous operation
- \*4: At RL = 7, 8
- \*5: T<sub>A</sub> <u>≤</u> +40 °C

#### • 256M-bit Sync. SRAM Type FCRAM

Supply Current Max. Initial Burst Clock Page Mode Supply Burst Mode Access Organization Access Access Power Voltage Frequency Part Number Standby Operating Time Time Time (W × b) Down Max. (MHz) (V) Max. (ns) Max. (ns) (mA) (µA) Max. (ns) \*<sup>3</sup> (μA) 1.75 to 6 \*<sup>4</sup> 250 \*5  $8M \times 32$ MB82DDS08314A-75L 45 N/A 135 40 10 1.95

\*1: Compliant with COSMORAM spec, with DDR Burst mode & Multiplexed Address and Data Bus

\*2: Shipping form: Chip, wafer

Package(115-pin FBGA) support for mass production is T.B.D.

- \*3: At Burst mode
- \*4: Data access time from CLK, CLK
- \*5: T<sub>A</sub> <u>≤</u> +40 °C

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#### \*1, \*2

\*1, \*2

\*1 \*2

# FCRAM<sup>™</sup> (Fast Cycle RAM) (3)



FCRAM is a trademark of Fujitsu Microelectronics Limited.

### ■ Consumer FCRAM<sup>TM</sup> (Fast Cycle RAM)

• 16M-bit SDR-SDRAM Type FCRAM

							*1, *2	
Organization		Clock	Clock Period	Access Time	Supply Curr	ent Max. * <sup>5</sup>	Supply Voltage (V)	
$(Bank \times W \times b)$	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * <sup>4</sup>	Operating (mA)	Standby (mA)		
	MB81ES171625-12	85	11.7	10.2	30	1	1.65 to 1.95	
$2\times512K\times16$	MB81ES171625-15	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES171625-15-X * <sup>3</sup>	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES173225-12	85	11.7	10.2	30	1	1.65 to 1.95	
$2\times256K\times32$	MB81ES173225-15	66.7	15	12	30	1	1.65 to 1.95	
	MB81ES173225-15-X * <sup>3</sup>	66.7	15	12	30	1	1.65 to 1.95	

\*1: Single Data Rate SDRAM Interface

\*2: Shipping form: Chip, wafer

\*3: Extended operating temperature

\*4: Access Time =  $t_{AC}$ \*5: Operating current is  $I_{DD1}$  (1 bank active) and Standby current is  $I_{DD2P}$  (Power down mode)

#### 64M-bit SDR-SDRAM Type FCRAM

Organization (Bank $\times$ W $\times$ b)		Clock	Clock Period	Access Time	Supply Cur	Supply		
	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * <sup>3</sup>	Operating (mA)	Standby (mA)	Voltage (V)	
	$4\times1M\times16$	O MB81ES641645A-07	135	7.4	6.5	T.B.D.	T.B.D.	1.7 to 1.95

○: New Product

\*1: Single Data Rate SDRAM Interface

\*2: Shipping form: Chip, wafer, 54-pin FBGA package

\*3: Access Time =  $t_{AC}$ 

#### 128M-bit SDR-SDRAM Type FCRAM

Organization (Bank $\times$ W $\times$ b)		Clock	Clock Period	Access Time	Supply Curr	Supply	
	Part Number	Frequency Max. (MHz)	Min. (ns)	Max. (ns) * <sup>3</sup>	Operating (mA)	Standby (mA)	Voltage (V)
$4\times1M\times32$	MB81ES123245-10	108	9.2	7	*5	0.5	1.7 to 1.9

\*1: Single Data Rate SDRAM Interface

\*2: Shipping form: Chip, wafer

\*3: Access Time = t<sub>AC</sub>

\*4: Operating current is I<sub>DD1</sub> (1 bank active) and Standby current is I<sub>DD2P</sub> (Power down mode)

\*5: 60 (256 page length), 45 (128 page Length), 35 (64 page length)

#### 256M-bit SDR-SDRAM Type FCRAM

							*1, *2
Organization		Clock	Clock Period Min. (ns)	Access Time	Supply Cur	Supply	
(Bank × W × b)	Part Number	Frequency Max. (MHz)		Max. (ns) * <sup>3</sup>	Operating (mA)	Standby (mA)	Voltage (V)
$4\times 2M\times 32$	© MB81ES253245	166	6	6	T.B.D.	T.B.D.	1.7 to 1.95

©: Under development

\*1: Single Data Rate SDRAM Interface

\*2: Shipping form: Chip, wafer

\*3: Access Time = t<sub>AC</sub>

\*1 \*2

\*1 \*0

# FRAM (Ferroelectric RAM)



### **FRAM**

	Organization		Access	Cycle	Clock	V <sub>CC</sub> Cı	urrent	Supply	Operating Temperature	F	Packag	es
Interface	(W × b)	Part Number	Max. (ns)	Min. (ns)	Max. (MHz)	Operating (mA)	Standby (µA)	Voltage (V)	Range T <sub>A</sub> (°C)	SOP	TSOP	FBGA
Parallel	32K × 8	MB85R256H	70	150	-	5	5	2.7 to 3.6	-40 to +85	28P	28P	-
Parallel	128K × 8	MB85R1001	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-
Parallel	64K × 16	MB85R1002	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	48P
Parallel	256K × 8	MB85R2001	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-
Parallel	128K × 16	MB85R2002	100	150	-	10	10	3.0 to 3.6	-20 to +85	-	48P	-
Serial	32K × 8	MB85RS256	-	-	15	5	3	3.0 to 3.6	-20 to +85	8P	-	-

Pakage : P - Plastic

#### EDID memory

Part Number	Memory	Organization	Interface	Supply Voltage	Packages
Part Number	Memory	(W × b)	internace	(V)	TSSOP
O MB85RF402	FRAM	256 $\times$ 8 For 4 DDC(I <sup>2</sup> C) ports		3.8 to 5.5	16P

○ : New released.

Pakage : P – Plastic

# Flash Memory (Single 1.8V)

SPANSION<sup>™</sup> Products



SPANSION<sup>™</sup> Products

### Flash memory (Single 1.8V)

		Access	Cycle	V <sub>CC</sub> Cu	rrent		Operating	Packages	
Organization (W × b)	Part Number	Time Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T <sub>A</sub> (°C)	TSOP	FBGA
1 M × 8	© S29AS008J50	50	50	16 (f = 5 MHz)	Б	1.65 to 1.95	-40 to +85	48P	48P
512 K × 16	© S29AS008J70	70	70		5				
2 M × 8	© S29AS016J50	50	50	16	5	1 65 to 1 05	40 to 195	400	19D
1 M × 16	© S29AS016J70	70	70	(f = 5 MHz)	5	1.05 10 1.95	-40 10 +85	401	401

☺: Under Developing

Package: P-Plastic

### Flash Memory (Single 3V)

SPANSION<sup>™</sup> Products



Variation PD: Automatic sleep mode PM: Page mode SRW: Simultaneous Read / Write operation (Read-while-program or Readwhile-Erase)

MirrorBit is a trademark of Spansion Inc.

```
*1: (16Kbytes × 1sectors) + (8Kbytes × 2sectors) + (32Kbytes × 1sector) + (64Kbytes × 7sectors)
```

```
*2: (16Kbytes × 1sectors) + (8Kbytes × 2sectors) + (32Kbytes × 1sector) + (64Kbytes × 15sectors)
```

```
*3: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 31sectors)
```

```
*4: (16Kbytes × 1sectors) + (8Kbytes × 2sectors + (32Kbytes × 1sector) + (64Kbytes × 61sectors)
```

```
*5 : (8Kbytes × 8sectors) + (64Kbytes × 63sectors)
```

```
*6 : (8Kbytes × 16sectors) + (64Kbytes × 126sectors)
```

```
*7 : (8Kbytes × 8sectors) + (64Kbytes × 127sectors)
```

```
*8 : (64Kbytes × 128sectors)
```

```
*9 : (8Kbytes × 16sectors) + (64Kbytes × 62sectors)
```

```
*10 : (8Kbytes \times 16sectors) + (64Kbytes \times 254sectors)
```

#### SPANSION<sup>™</sup> Products

### Flash memory (Single 3V)

		Access	Cycle	V <sub>CC</sub> Cu	rrent		Operating	Pa	ackage	s
Organization (W × b)	Part Number	Time Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T <sub>A</sub> (°C)	TSOP	FBGA	SOP
512K × 8	S29AL004D70 *	70	70	16	5	27 to 36	-40 to ±85	48P	48P	44P
256K × 16	S29AL004D90	90	90	(f = 5 MHz)	5	2.7 10 0.0	10 10 100	401		171
	S29AL008D70 *	70	70	16	5	27 to 36	-40 to +85	48P	48P	44P
$1M \times 8$	S29AL008D90	90	90	(f = 5 MHz)	Ŭ	2.7 10 0.0		101	101	
512K × 16	© S29AL008J45	45	45	16	5	27 to 36	-40 to +85	48P	48P	44P
	© S29AL008J55	55	55	(f = 5 MHz)	0	2.7 10 0.0	40 10 100	-101	-101	
	S29AL016D70 *	70	70	16	5	27 to 36	-40 to +85	48P	48P	_
$2M \times 8$	S29AL016D90	90	90	(f = 5 MHz)	5	2.7 10 0.0	-40 10 +00	401	101	
1M × 16	© S29AL016J45	45	45	16	5	27 to 36	-40 to ±85	48P	48P	
	© S29AL016J55	55	55	(f = 5 MHz)	5	2.7 10 0.0	-40 10 403		401	446
	S29AL032D70 *	70	70	16	5	27 to 36	-40 to +85	48D	18D	18D
-	S29AL032D90	90	90	(f = 5 MHz)	5	2.7 10 0.0	-40 10 403	401	401	401
	S29JL032H70	70	70	16	5	27 to 36	-40 to +85	48D		
4M  imes 8	S29JL032H90	90	90	(f = 5 MHz)	5	2.7 10 0.0	-40 10 +03	401		
2M × 16	S29PL032J55	55	55		5					
	S29PL032J60	60	60	30		2.7 to 3.6	-45 to +85	_	48P 56P	-
	S29PL032J65	65	65	(f = 5 MHz)						
	S29PL032J70	70	70							
	S29JL064H70	70	70	16	5	27 to 36	-40 to ±85	48P	_	_
	S29JL064H90	90	90	(f = 5 MHz)	5	2.7 10 0.0	-40 10 +00	401		
8M  imes 8	S29PL064J55	55	55							
4M × 16	S29PL064J60	60	60	30	5	27 to 36	-45 to +85	_	48P	_
	S29PL064J65	65	65	(f = 5 MHz)	5	2.7 10 0.0	-43 10 +03		56P	
-	S29PL064J70	70	70							
	S29PL127J55	55	55			27 to 36				
8M × 16	S29PL127J60	60	60	30	5	2.7 to 3.6	-45 to +85	56P	50P	_
	S29PL127J65	65	65	(f = 5 MHz)	5	2.7 to 3.6 1.65 to 1.95		501	501	
-	S29PL127J70	70	70							

©: Under Developing

<sup>\* :</sup> at C<sub>L</sub> = 30pF

## Flash Memory (MirrorBit<sup>™</sup>) (Single 3 V)



Variation
PD : Automatic sleep mode
PM: Page mode
WB: Write buffer

MirrorBit is a trademark of Spansion Inc.

\*1: Uniform sector model : 32Kword (64Kbytes) × 64sectors

Boot sector model : 32Kword (64Kbytes) × 63sectors + 4Kword (8Kbytes) × 8sectors

- \*2: Uniform sector model : 32Kword (64Kbytes) × 128sectors
- Boot sector model : 32Kword (64Kbytes) × 127sectors + 4Kword (8Kbytes) × 8sectors
- \*3: Sector structure 64Kword (128Kbytes) × 128sectors
- \*4: Sector structure 64Kword (128Kbytes)  $\times$  256sectors
- \*5: Sector structure 64Kword (128Kbytes)  $\times$  512sectors
- \*6: Sector structure 64Kword (128Kbytes) × 1024sectors

#### SPANSION<sup>™</sup> Products

### Flash memory (MirrorBit ) (Single 3V)

		Access Cycle V <sub>CC</sub> Currer		rrent		Operating	Pack	ages	
Organization (W × b)	Part Number	Time Max. (ns)	Time Min. (ns)	Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T <sub>A</sub> (°C)	TSOP	FBGA
	S29GL032A90	90 (25)	90					40P	
4M ~ 8	S29GL032A10	100 (30)	100	25 (f = 5 MHz)	5	3.0 to 3.6	-40 to +85	48P	48P 64P
2M × 16	S29GL032A11	110 (30)	110					56P	
	S29GL032N90	90 (25)	90	40 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P 56P	48P 56P
	S29GL064A90	90 (25)	90						
8M × 8	S29GL064A10	100 (30)	100	25 (f = 5 MHz)	5	3.0 to 3.6	-40 to +85	48P 56P	64P
4M × 16	S29GL064A11	110 (30)	110						
	S29GL064N90	90 (25)	90	40 (f = 5 MHz)	5	2.7 to 3.6	-40 to +85	48P 56P	48P 56P
	S29GL128N90	90 (25)	90			3.0 to 3.6			
	S29GL128N10	100 (25)	100	50 (f = 5 MHz)	5	-40 to +85		56P	64P
16M × 8	S29GL128N11	110 (30)	110	. ,		2.7 10 0.0			
8M × 16	S29GL128P90	90 (25)	90	50		3.0 to 3.6	0 to +70 -40 to +85		
	S29GL128P10	100 (25)	100	(f = 5 MHz)	5	27 to 36	-40 to +85	56P	64P
	S29GL128P11	110 (25)	110			2.7 10 0.0	40 10 100		
	S29GL256N90	90 (25)	90		5	3.0 to 3.6			
	S29GL256N10	100 (25)	100	50 (f = 5 MHz)		2.7 to 3.6	-40 to +85	56P	64P
32M × 8	S29GL256N11	110 (30)	110			2.7 10 0.0			
16M × 16	S29GL256P90	90 (25)	90	50		3.0 to 3.6	0 to +70 -40 to +85		
	S29GL256P10	100 (25)	100	(f = 5 MHz)	5	27 to 36	-40 to +85	56P	64P
	S29GL256P11	110 (25)	110			2.7 10 0.0			
	S29GL512N10	100 (25)	100	50	5	2.7 to 3.6	-40 to +85	56P	64P
	S29GL512N11	110 (30)	110	(f = 5 MHz)	-				•
$\begin{array}{c} 64M\times 8\\ 32M\times 16\end{array}$	S29GL512P10	100 (25)	100	50		3.0 to 3.6	0 to +70 -40 to +85		
-	S29GL512P11	110 (25)	110	(f = 5 MHz)	5	27 to 36	-40 to +85	56P	64P
	S29GL512P12	120 (25)	120			2.7 10 0.0	+0 10 +00		
128M × 8	S29GL01GP11	110 (25)	110	50		3.0 to 3.6	0 to +70 -40 to +85		
64M × 16	S29GL01GP12	120 (25)	120	(f = 5 MHz)	Iz) 5	27 to 36	-40 to ±85	56P	64P
	S29GL01GP13	130 (25)	130			2.7 10 0.0	10 10 103		

Memory

C<sub>L</sub> = 30pF Package: P-Plastic

## Flash Memory (MirrorBit<sup>™</sup>) (Single 1.8V)



Variation	
PD: Auto	omatic sleep mode
BM: Burs	st mode
SRW: Sir	multaneous Raad/Write operation
	(Read-while-program or Read-while-Erase)
HM: Han	d Shake Mode

- \*1 : 16 Kword  $\times$  8sectors + 64 Kword  $\times$  126sectors
- \*2 : 16 Kword  $\times$  8sectors + 64 Kword  $\times$  254sectors
- \*3 : 16 Kword  $\times$  8sectors + 64 Kword  $\times$  510sectors

MirrorBit is a trademark of Spansion Inc.

#### SPANSION<sup>™</sup> Products

### Flash memory (MirrorBit ) (Single 1.8V)

Organization (W × b)	Part Number	Access Time Max. (ns)	Burst Speed (MHz)	V <sub>CC</sub> Current			Operating	Packages
				Read (mA)	Standby Mode (µA)	Supply Voltage (V)	Temperature Range T <sub>A</sub> (°C)	FBGA
8 M × 16	S29WS128N0LBxW	80 * <sup>1</sup> 80/13.5 * <sup>2</sup>	54	36 * <sup>3</sup>	70	1.70 to 1.95	-25 to +85	84P
	S29WS128N0PBxW	80 * <sup>1</sup> 80/11.2 * <sup>2</sup>	66	42 * <sup>3</sup>				
	S29WS128N0SBxW	80 * <sup>1</sup> 80/9.0 * <sup>2</sup>	80	48 * <sup>3</sup>				
	S29WS128P0LBxW	80 * <sup>1</sup> 80/13.5 * <sup>2</sup>	54	39 * <sup>3</sup>				
	S29WS128P0PBxW	80 * <sup>1</sup> 80/11.2 * <sup>2</sup>	66	43 * <sup>3</sup>				
	S29WS128P0SBxW	80 * <sup>1</sup> 80/9.0 * <sup>2</sup>	80	48 * <sup>3</sup>				
	S29WS128PABBxW	80 * <sup>1</sup> 80/7.6 * <sup>2</sup>	108	54 * <sup>3</sup>				
16 M × 16	S29WS256N0LBxW	80 * <sup>1</sup> 80/13.5 * <sup>2</sup>	54	36 * <sup>3</sup>	70	1.70 to 1.95	-25 to +85	84P
	S29WS256N0PBxW	80 * <sup>1</sup> 80/11.2 * <sup>2</sup>	66	42 * <sup>3</sup>				
	S29WS256N0SBxW	80 * <sup>1</sup> 80/9.0 * <sup>2</sup>	80	48 * <sup>3</sup>				
	S29WS256P0LBxW	80 * <sup>1</sup> 80/13.5 * <sup>2</sup>	54	39 * <sup>3</sup>				
	S29WS256P0PBxW	80 * <sup>1</sup> 80/11.2 * <sup>2</sup>	66	43 * <sup>3</sup>				
	S29WS256P0SBxW	80 * <sup>1</sup> 80/9.0 * <sup>2</sup>	80	48 * <sup>3</sup>				
	S29WS256PABBxW	80 * <sup>1</sup> 80/7.6 * <sup>2</sup>	108	54 * <sup>3</sup>				
32 M × 16	S29WS512P0LBxW	80 * <sup>1</sup> 80/13.5 * <sup>2</sup>	54	36 * <sup>3</sup>	70	1.70 to 1.95	-25 to +85	84P
	S29WS512P0PBxW	80 * <sup>1</sup> 80/11.2 * <sup>2</sup>	66	43 * <sup>3</sup>				
	S29WS512P0SBxW	80 * <sup>1</sup> 80/9.0 * <sup>2</sup>	80	48 * <sup>3</sup>				
	S29WS512PABBxW	80 * <sup>1</sup> 80/7.6 * <sup>2</sup>	108	54 * <sup>3</sup>				

 $C_L = 30 pF$ 

Package: P-Plastic

\*1: Asynchronous access time

\*2: Synchronous delay time/burst access time

\*3: At burst read Continuous mode (Max.)

# Serial Peripheral Interface (MirrorBit<sup>™</sup>) (Single 3V)



Variation SI: Serial interface

\*1 : Sector structure - 512 K bits  $\times$  8 sectors or 128 K bits  $\times$  2 sectors + 32 K bits  $\times$  2 sectors + 16 K bits  $\times$  2 sectors + 512 K bits  $\times$  7 sectors

- \*2 : Sector structure 512 K bits  $\times$  16 sectors
- \*3 : Sector structure 512 K bits  $\times$  32 sectors
- \*4 : Sector structure 512 K bits  $\times$  64 sectors

\*5 : Sector structure - 512 K bits  $\times$  128 sectors

\*6 : Sector structure - 512 K bits  $\times$  256 sectors

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#### SPANSION<sup>™</sup> Products

## Flash memory (MirrorBit) (Single 3V)

Organization (W × b)		Clock	v <sub>cc</sub> c	urrent	Supply	Operating Temperature	Packages	
	Part Number	speed (MHz)	Read (mA)	Standby Mode (µA)	Voltage (V)	Range T <sub>A</sub> (°C)	SOIC	SON
4  M  imes 1	S25FL040A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8	USON8
8 M × 1	S25FL008A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8	USON8
16 M × 1	S25FL016A	50	19 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC8 SOIC16	WSON8
32 M × 1	S25FL032A	50	19 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC16	_
64  M  imes 1	S25FL064A	50	13 (f = 50MHz)	50	2.7 to 3.6	-40 to +85	SOIC16	_
128 M × 1	S25FL128P	104	22 (f = 104MHz)	200	2.7 to 3.6	-40 to +85	SOIC16	WSON

 $C_L = 30 pF$ 

Package: P-Plastic

# Flash Memory (MirrorBit<sup>™</sup> ORNAND<sup>™</sup>) (Single 1.8V)



Variation ND: NAND interface

\* : Block size 128 K + 4 Kbyte

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## Flash memory (MirrorBit ORNAND) (Single 1.8V)

Organization (W × b)		Page	Serial	V <sub>CC</sub> Current			Operating	Packages	
	Part Number	Access (μs)	Read (ns)	Read (mA)	Standby Mode (μΑ)	Supply Voltage (V)	Temperature Range T <sub>A</sub> (°C)	TSOP	BGA
64 M × 8	S30MS512P25BFW00	8	25	45	60	1.70 to 1.95	-25 to +85	48P	137P
	S30MS512P25TFW00	8	25	4					10/1
	O S30MS512R25TFW00	8	30	50					_
	O S30MS01GR25TFW01	8	30	50					_
	S30MS512P25BFW01	8	25	45	60	1.70 to 1.95	-25 to +85	48P	137D
$32 \text{ M} \times 16$	S30MS512P25TFW01	8	25	40					1071
	O S30MS512R25TFW01	8	30	50					-
	S30MS01GP25BFW00	8	25	45	60	1.70 to 1.95	-25 to +85	48P	137D
100 M \. 0	S30MS01GP25TFW00	8	25	40					1571
120 IVI × 0	O S30MS01GR25TFW00	8	30	50					
	O S30MS02GR25TFW01	8	30	50					-
64 M × 16	S30MS01GP25BFW01	8	25	45	60	1 70 to 1 95	-25 to +85	18D	137D
04 IVI × 10	S30MS01GP25TFW01	8	25	45	00	1.70 10 1.95	-20 10 +00	40	107
256 M × 8	○ S30MS02GR25TFW00	8	30	50	60	1.70 to 1.95	-25 to +85	48P	-

 $\bigcirc: \text{New Product}$ 

Package: P-Plastic

 $C_L = 30 pF$ 

The productions listed below are scheduled to go out of production. If you are considering the use in the new applications, select the other series of products

## **FCRAM**

Part number	Description
MB82DP02183C-65L	32 Mbit Async. SRAM Type FCRAM
MB82DBS02163C-70L	32 Mbit Async./Sync. SRAM Type FCRAM
MB82DP04183C-65L	64 Mbit Async. SRAM Type
MB82DP04183D-65L	FCRAM
MB82DBS04163C-70L	64 Mbit Async./Sync. SRAM Type
MB82DBS04163D-70L	FCRAM
MB82DBS04314C-70L	128 Mbit Async./Sync. SRAM Type FCRAM

# **ASIC Product Line-up**

## ASIC Products

					Page	No.
ASIC Products	Standard cell	CMOS		CS201 series	with on-chip RAM, ROM, ADC/DAC	74
				CS101 series	More than 91,000,000 (on-chip) gates with on-chip RAM, ROM, ADC/DAC	75
				CS91 series	with on-chip RAM, ROM, Multipliers, ADC/DAC	76
				CS86 series	More than 40,000,000 (on-chip) gates with on-chip RAM, ROM, FIFO, Delay Line, ADC/DAC	77
			_	CS81 series	More than 40,000,000 (on-chip) gates, 11 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	78
				CS66 series	More than 1,700,000 (on-chip) gates, 98 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	79
	Macro-embedded type cell arrays	CMOS		CE81 series	Maximum of 34,000,000 (on chip) gates, 12 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	81
				CE77 series	Maximum of 10,000,000 (on chip) gates, 33 ps/gate with on-chip RAM, ROM, FIFO, Delay Line	82
				CE71 series	Maximum of 8,096,000 (on chip) gates, 29 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC	84
				CE66 series	Maximum of 1,138,000 (on-chip) gates, 98 ps/gate with on-chip RAM, ROM, Multipliers, ADC/DAC.	86
				CE61 series	Maximum of 2,025,000 (on chip) gates, 85 ps/gate with on-chip RAM/ROM, Multipliers, ADC/DAC	88
	Gate arrays	Sea-of-Gate CMOS		CG61 series	Maximum of 1,568,000 (on chip) gates, 85 ps/gate with on-chip RAM, Analog PLL embedment is possible in some frames	90
				CG47 series	Maximum of 55,000 (on chip) gates, 300 ps/gate with on-chip RAM, FIFO	91
				CG46 series	Maximum of 198,000 (on chip) gates, 300 ps/gate with on-chip RAM, FIFO	92

## CS201 Series

#### Features

Technology : 65 nm Si-gate CMOS 6- to 12-metal layers. Low-k (low permittivity) inter-layer insulation film material is used for all layers. Consolidation of all 3 kinds of set of cell (energy-saving version to high-velocity version) is possible. Supply voltage : +1.2 V  $\pm$  0.1 V , +1.0 V  $\pm$  0.1 V Junction temperature range : -40 °C to +125 °C Reduced chip sized realized by I/O with pad. Supports a wide range of cell sets (from low power versions to high speed versions) IP macros : CPU (ARM11, ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM and others) It supports energy-saving mode, multi mode SRAM. It supports energy-saving technology "CoolAdjust"\* Supports large capacity memory (1T-SRAM-Q) High-speed interface macro (up to 10 Gbps) Special interfaces (LVDS, SSTL and others) Supports use of industry standard libraries (. LIB) Uses industry standard tools and supports the optimum tools for the application. High reliability design estimation in the early stage of physical design realized by physical prototyping tool. Layout synthesis with optimized timing realized by physical synthesis tools. Hierarchical design environment for supporting large-scale circuits. High accuracy design environment considering dynamic drop in power supply voltages, signal noise, delay penalty, and crosstalk. I/O design environment (power line design, assignment and selection of I/Os, package selection) considering noise. Supports static timing sign-off Improved timing settling by introducing Statistical Timing Analysis (SSTA). Steady product supply and countermeasure for diffusion by introduction of DFM Supports memory (RAM/ROM) BIST Supports boundary SCAN Supports LOGIC BIST Supports transition delay test Optimum of package lineup : TEBGA, FBGA, PBGA, FC-BGA \*: "CoolAdjust" is a generic name of Fujitsu Microelectronics's energy-saving technology

## CS101 Series

## Features

reatures	
Optimum gate count	: Maximum of 91,000,000 gates
Technology	: 90 nm Si-gate CMOS
	6- to 10-metal layers. Low-k (low permittivity) inter-layer insulation film material is
	used for all layers.
	3 types of transistors (low leak, standard, high speed) can be mixed on a chip.
	The design rules comply with industry standard processes.
Supply voltage	: +1.2 V $\pm$ 0.1 V, +1.0 V $\pm$ 0.1 V
Junction temperature range	: -40 °C to +125 °C (normal)
Gate delay time	: tpd = 12 ps (1.2 V, Inverter, F/O = 1)
Gate power consumption	: Pd = 2.7 nW/MHz/BC (1.2 V, Inverter, F/O = 1)
Reduced chip sized realized	by I/O with pad.
Supports a wide range of ce	Il sets (from low power versions to high speed versions)
Compliance with industry sta	andard design rules enables non-Fujitsu commercial macros to be easily incorporated.
IP macros	CPU (ARM9, ARM7 I DMI), DSP, PGI, IEEE 1394, USB, IFDA, PLL, ADG, DAG, and others
Complied Cells (RAM/ROW a	(up to 10 Ohno)
High-speed Interface macro	(up to 10 Gbps)
Special Interfaces (LVDS, St	siL_2 and others)
Supports use of industry sta	ndard libraries (. LIB)
Uses industry standard tools	and supports the optimum tools for the application.
Layout synthesis with optimi	and timing realized by physical design realized by physical prototyping tool.
Hierarchical design environ	nent for supporting large-scale circuits
High accuracy design environ	ment for supporting large-scale circuits.
crosstalk	The solution of the second state of the second
I/O design environment (pov	ver line design, assignment and selection of I/Os, package selection) considering noise.
Supports static timing sign-c	off
Supports memory (RAM/RC	IM) BIST
Supports boundary SCAN	
Supports LOGIC BIST	
Supports transition delay tes	st
Optimum of package lineup	: TEBGA, FBGA, PBGA, FC-BGA

## CS91 Series

#### Features

Optimum gate count : Maximum of 48,000,000 gates Technology : 0.11 µm Si-gate CMOS, 5- to 8-layer wiring (Copper is used as wire material), Low-k Inter-laver material (Inter-layer material that has low permittivity) Supports 8 types of cell sets that differ in speed, integration, and power consumption. These cell sets can be mixed on a chip. : +1.2 V ± 0.1 V (normal) Supply voltage Junction temperature range : -40 to +125 °C tpd = 16 ps (1.2 V, Inverter, F/O = 1) Gate delay time : : Pd = 6.6 nW/MHz (1.2 V, Inverter, F/O = 1) Gate power consumption High-speed interface macro (up to 10 Gbps) Special interfaces: P-CML, LVDS, PCI, USB, SSTL, HSTL, T-LVTTL, and others Buffer cells for crystal oscillation circuits. : CPU (ARM9, ARM7TDMI), DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others IP macros Compiled cells (RAM/ROM/multiplier and others) Uses industry standard tools and supports the optimum tools for the application. Short-term development using a physical prototyping tool. Hierarchical design environment for supporting large-scale circuits. Supports Signal Integrity, EMI noise reduction Supports High resolution RC extraction base delay calculation environment Supports optimization environment of power supply wire Supports static timing sign-off Supports memory (RAM/ROM) BIST Supports boundary SCAN Supports LOGIC BIST Supports transition delay test A variety of package options : FC-BGA (Max. 2116 pin), EBGA, HQFP, FBGA and others

CS86 Series	
Features	
Optimum gate count Technology	<ul> <li>Maximum of 40,000,000 gates</li> <li>0.18 μm Si-gate CMOS, 4- to 6-layer wiring Supports three types of internal cell sets (ultra high-speed, standard, low-leak) Capable of integrating a mixture of standard transistor cell and ultra high-speed process/cell, and mixture of standard transistor cell and low leak process/cell on a single</li> </ul>
	chip
Supply voltage Gate delay time	: $+1.8 V \pm 0.15V$ (normal) to $+1.1V \pm 0.1V$ : tpd = 88 ps (standard : 1.8 V, 2NAND, F/O = 2, standard load) tpd = 70 ps (ultra high-speed : 1.8 V, 2NAND, F/O = 2, standard load) tpd = 136 ps (low-leak : 1.8 V, 2NAND, F/O = 2, standard load)
Leakage Current	: 0.023 nW (standard : 1.8 V, 2NAND, F/O = 0, no load) 3.922 nW (ultra high-speed : 1.8 V, 2NAND, F/O = 0, no load) 0.0067 nW (low-leak : 1.8 V, 2NAND, F/O = 0, no load)
Gate power consumption	: 40.1 nW/MHz (standard : 1.8 V, 2NAND, $F/O = 1$ , 4Grid) 42.7 nW/MHz (ultra high-speed : 1.8 V, 2NAND, $F/O = 1$ , 4Grid) 38.3 nW/MHz (low-leak : 1.8 V, 2NAND, $F/O = 1$ , 4Grid)
Junction temperature rang	e:-40 to +125 °C
Output buffer cells with noi	se reduction circuits
Inputs with on-chip input p	ull-up/pull-down resistors and bidirectional buffer cells.
Buffer cells for crystal osci	lation circuits.
Special interfaces	: SSTL2, PCI, P-CML, T-LVTTL, USB2.0, IEEE1394, and others
IP macros	: CPU (FR-V, ARM9, and others), DSP, PCI, IEEE1394, USB2.0, IrDA, PLL, ADC, DAC,
Compiled cells (RAM/ROM Configurable internal bus of	and others I/FIFO/Delay line, and others) sircuits
Short-term development u	Rivare co-design environment
Low-power dissipation usin	a a low nower synthesis tool
Short-term development u	sing a timing driven layout tool
Hierarchical design enviror	nment for supporting large-scale circuits
Supports signal Integrity	
Supports memory (RAM, F	ROM) SCAN
Supports memory (RAM) I	BIST
Supports boundary SCAN	
Supports path delay test	
Supports transition delay to	
A variety of package option	is (UFF, IUFF, LUFF, HUFF, MUA, MUA, MUA, MUA, EDUA)

Note: Some items are in preparation.

Packages The table below lists the available package types.

Туре	Pin Count	Material
QFP	176, 208, 240	Plastics
TQFP	100, 120	Plastics
LQFP	144, 176, 208, 256	Plastics
HQFP	208, 240, 256, 304	Plastics
PBGA	256, 352, 420	Plastics
FBGA	112, 144, 168, 176, 192, 224, 272, 288, 240, 304, 368	Plastics
FLGA	144, 176, 208, 224, 288	Plastics
EBGA	660	Plastics

Note: This list contains packages under planning. Contact Fujitsu Microelectronics for the availability.

## CS81 Series

Features Optimum gate count : Maximum of 40,000,000 gates : 0.18 µm Si-gate CMOS, 3- to 6-layer wiring Technology Capable of integrating a mixture of high-speed processes and cells on a single chip Supply voltage : +1.8 V  $\pm$  0.15V (normal) to +1.1V  $\pm$  0.1V : tpd = 11 ps (1.8 V, Inverter, F/O = 1) Gate delay time Gate power consumption : 5nW/MHz/BC (1.1V, 2NAND, F/O = 1) Junction temperature range : -40 to +125 °C High-speed interface macro (up to 3.125 Gbps) Output buffer cells with noise reduction circuits Inputs with on-chip input pull-up/pull-down resistors (33 k $\Omega$  typical) and bidirectional buffer cells. Buffer cells for crystal oscillation circuits. Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM/multiplier, and others) Configurable internal bus circuits Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool Supports static timing sign-off Dramatically reducing the time for generating test vectors for timing verification and the simulation time Hierarchical design environment for supporting large-scale circuits Simulation (before layout) considering the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture. Supports signal Integrity, EMI noise reduction Supports memory (RAM, ROM) SCAN Supports memory (RAM) BIST Supports boundary SCAN Supports At-Speed test on internal circuits Supports path delay test Supports transition delay test A variety of package options (TQFP, HQFP, EBGA, FBGA, TAB-BGA, FC-BGA, LQFP)

Note: Some items are in preparation.

#### Packages

The table below lists the available package types.

Туре	Pin Count	Material
TAB-BGA	304, 352, 480 560, 660, 720	Plastics
EBGA	576, 660, 672	Plastics
HQFP	208, 240, 256, 304	Plastics
TQFP	100, 120	Plastics
LQFP	144, 176, 208	Plastics
FBGA	288	Plastics
FC-BGA	1089, 1225, 1369, 1681, 1849, 2116	Plastics, Ceramic

Note: This list contains packages under planning. Contact Fujitsu Microelectronics for the availability.

## CS66 Series

## Features

culuico	
Optimum gate count	: Maximum of 1,700,000 gates
Technology	: 0.35 μm Si-gate, 3- to 4-layer metal wiring
Supply voltage	: +3.3 V $\pm$ 0.3 V (normal) to +2.0 V $\pm$ 0.1 V
	+5.0 V $\pm$ 10% (only for external interface; when internal requirements is 3.3 V)
	+3.3 V $\pm$ 10% (only for external interface; when internal requirements is 3.3 to 2.0 V)
Gate delay time	: t <sub>pd</sub> = 91 ps (high-speed type, F/O = 2, standard load)
Gate power consumption	: 0.29 $\mu$ W/MHz (F/O = 2, standard load)
Junction temperature range	: -40 to +125°C
High-load driving capability	: I <sub>OL</sub> = 2 mA/4mA/8mA/12mA/24mA mixable.
Output buffer cells with noise	e reduction circuits
On-chip input pull-up/pull-do	wn resistors (50 k $\Omega$ typical)
Buffer cells for crystal oscilla	ation circuits.
Configurable internal bus cir	cuits
Highly integrated RAM/ROM	I/multipliers mountable; arbitrary words/bits configurable.
Clock skew layout design me	ethod (Cadence "CT-Gen") based on the floor plan information minimizes post-layout
circuit modification, reducing	turnaround time for development.
Simulation (before layout) co	onsidering the input through rate and detailed RC delay calculation (after layout),
supporting development with	n minimized timing trouble after trial manufacture.
Special interface (T-LVTTL a	nd SDRAM-I/F, and others)
Analog PLL	
Analog circuits (ADC, DAC,	OPAMP and others)
Macros for system ASICs (C	PU core, CPU peripheral, operation macro, and others)
Supports DFF scan test with	1 MUX
Supports memory (RAM/RC	IM) scan
Supports memory (RAM) BI	ST
Supports boundary SCAN	
Note: Some items are in pre	naration
note. Some items are in pre	

Number of gates used in each package The table below lists the available package types and the reference number of gates used. CS66 (P-frame)

Package and pin count		0 2000K 4000K 6000K 8000K 10000K 12000K 14000K 1 	6000K
TQFP	100		– 1579K
LQFP	100 144 176 208	1305K	– 1579K – 1579K – 1579K
QFP	120 144 160 176 208 240 256		– 1579K – 1579K – 1579K – 1579K – 1579K – 1579K – 1579K – 1579K
HQFP	208 240 256 304		– 1579K – 1579K – 1579K – 1579K
PBGA	256 352		– 1579K – 1579K
FBGA	112 144 168 176 192 224 288	639K 639K 835K 1305K	– 1579K – 1579K – 1579K
Note:	This list	contains packages under planning.	

#### CS66 (S-frame)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K	
TQFP	100	158K	
LQFP	100 144 208	158K 158K 433K	
QFP	120 144 160 176 208 240	158K 158K 228K 228K 228K 545K	
HQFP	208 240 256		
PBGA	256 352	545K 807K	
FBGA	112 144 168 176 192 224 288	<u>— 192K</u> 228K 433K <u>— 228K</u> 289K 433K 807K	

## CE81 Series

#### Features

High Integration : Maximum of 34,000,000 BCs Technology : 0.18 µm Si-gate CMOS, 4- to 5-layer wiring Supply voltage : +1.8 V  $\pm$  0.15 V (normal) to +1.1 V  $\pm$  0.1 V Gate delay time : tpd = 12 ps (1.8V, Inverter, F/O = 1)Gate power consumption : 8nW/MHz/BC (1.1V, 2NAND, F/O = 1) Junction temperature range : -40 to +125 °C Output buffer cells with noise reduction circuits Inputs with on-chip input pull-up/pull-down resistors (33 k $\Omega$  typical) and bidirectional buffer cells. Buffer cells for crystal oscillation circuits. Special interfaces: P-CML, LVDS, PCI, AGP, USB, SDRAM-I/F, SSTL, and others IP macros: CPU, DSP, PCI, IEEE1394, USB, IrDA, PLL, ADC, DAC, and others Compiled cells (RAM/ROM/multipliers, and others) Configurable internal bus circuits Advanced for hardware/software co-design environment Short-term development using a timing driven layout tool Supports static timing sign-off Dramatically reducing the time for generating test vectors for timing verification and the simulation time. Hierarchical design environment for supporting large-scale circuits Supports optimization environment of power supply wire Simulation (before layout) considering of the input through rate and high resolution RC extraction base delay calculation (after layout), supporting development with minimized timing trouble after trial manufacture. Supports Signal Integrity Supports memory (RAM, ROM) SCAN Supports memory (RAM) BIST Supports boundary SCAN Supports At-Speed test on internal circuits Supports path delay test Supports transition delay test A variety of package options (TQFP, HQFP, EBGA, FBGA, TAB-BGA, LQFP) Note: Some items are in preparation.

## Number of gates used in package

The table below lists the available package types and the reference number of gates used.

Package and pin count		о 2000К 4000К 6000К 8000К 10000К 12000К 14000К 16000К	J
TAB-BGA	304 352 480 560 660 720	— 891К — 1254К — 1905К — 2689К — 3609К 9129К	
EBGA	576 660 672	5982K 9805K 7952K	
HQFP	208 240 256 304 304	<u>— 1098K</u> <u>2085K</u> <u>3764K</u> <u>4712K</u> 15158K	
TQFP	100 120	— 514K — 514K	
LQFP	144 176 208	722K 722K 1098K	
FBGA	288	4712K	

## CE77 Series

### **Features**

Valui VV	
High integration	: Maximum of 10,000,000 BCs
Technology	: 0.25 μm Si-gate CMOS, 3- to 4-layer wiring
Supply voltage	: +2.5 V $\pm$ 0.2 V (normal) to +1.5 V $\pm$ 0.1 V
Junction temperature range	: -40 to +125°C
Gate delay time	: t <sub>pd</sub> = 33 ps (2.5 V, Inverter, F/O = 1, No load)
Gate power consumption	: 0.02 $\mu$ W/MHz (1.5 V, Inverter, F/O = 1, No load)
High-load driving capability	: I <sub>OL</sub> = 2mA/4mA/8mA/12mA mixable.
Output buffer cells with noise	eduction circuits
Inputs with on-chip input pull	-up/pull-down resistors (25 k $\Omega$ typical) and bidirectional buffer cells.
Buffer cells for crystal oscilla	tion circuits.
Special interfaces (P-CML, L	VDS, T-LVTTL, SSTL, PCI, USB, GTL+, and others)
IP macros (CPU, PCI, USB,	IrDA, PLL, DAC, ADC, and others)
Compiled cells (RAM/ROM/F	FIFO/Delay Line, and others)
Configurable internal bus cire	cuits
Advanced for hardware/softw	vare co-design environment
Short-term development usir	ng a timing driven layout tool
Hierarchical design environm	nent for supporting large-scale circuits
Supports static timing sign-o	ff
Dramatically reducing the tim	ne for generating test vectors for timing verification and the simulation time.
Simulation (before layout) co	nsidering the input through rate and detailed RC delay calculation (after layout),
supporting development with	minimized timing trouble after trial manufacture.
Supports memory (RAM, RC	)M) SCAN
Supports memory (RAM) BIS	ST
Supports boundary SCAN	
Supports path delay test	
A variety of package options	(SQFP, LQFP, HQFP, FBGA, PBGA)

Note: Some items are in preparation.

Number of gates used in each package The table below lists the available package types and the reference number of gates used.

CE77 (V-Frame)

Package and pin count		0 1000k 2000k 3000k 4000k 5000k 6000k 7000k 8000k 9000k	Material
SQFP	176 208 240		P P P
HQFP	208 240 256 304	1776k 2276k 1776k 7128k	P P P
PBGA	256	618k	Р

P: Plastic

Package and pin count		о 500К 1000К 1500К 2000К 2500К 3000К 3500К 4000К 4500К 5000К	Material
LQFP	144 176 208 256	976 K 	P P P P
HQFP	208 240 256 304	1375 К 1609 К 2109 К 4538 К	P P P P
FBGA	144 176 224 288	461 К 646 К 1375 К 2109 К	P P P P
PBGA	256 352 420	1841 К 2678 К 3789 К	P P P

#### CE77 (T-Frame)

P: Plastic

## CE71 Series

### Features

eatures	
High integration	: Maximum of 8,000,000 BCs
Technology	: 0.25 μm Si-gate CMOS, 3- to 4-layer metal wiring
Supply voltage	: +2.5 V ± 0.2 V (normal) to +1.5 V ± 0.1 V
	(5 V TTL interface is available if 5 V tolerant I/O is adopted. Some frames are under
	development.)
Gate delay time	: t <sub>pd</sub> = 29 ps (2.5 V, Inverter, F/O = 1, No load)
Gate power consumption	: 0.060 μW/MHz (F/O = 1, No load)
Junction temperature range	: -40 to +125°C
High-load driving capability	: I <sub>OL</sub> = 2 mA/4 mA/8 mA/12 mA mixable.
Output buffer cells with noise	e reduction circuits
Inputs with on-chip input pul	I-up/pull-down resistors (25 k $\Omega$ typical) and bidirectional buffer cells.
Buffer cells for crystal oscilla	ation circuits.
Special interfaces (P-CML, I	_VDS, SDRAM-I/F, SSTL, and others)
IP macros (SPARClite, FR40	), F <sup>2</sup> MC16LX, PCI, IEEE1394, USB, IrDA, PLL, ADC/DAC, and others)
Compiled cells (RAM/ROM/	nultipliers, and others)
Configurable internal bus cir	cuits
Advanced for hardware/softwa	ware co-design environment
Linking floor plan tools and I	ogic synthesis tools allows automatic optimization of the circuits using the floor plan
information. The Clock Drive	n Design Method (CDDM) clock tree synthesis tools using the floor plan information are
also available. Using the floc	r plan information in the pre-layout stage would eliminate the problems of setup after lay-
out or timing problems for he	old, significantly reducing the time to market.
Supports the static timing si	gn off using the Synopsys CAD tool Prime Time. This contributes to the considerable
reduction of time required fo	r test vector creation for timing verification and the simulation time.
Simulation (before layout) co	onsidering the input through rate and detailed RC delay calculation (after layout),
supporting development with	n minimized timing trouble after trial manufacture.
Supports memory (RAM, RC	JM) SCAN
Supports memory (RAM) BI	SI
Supports boundary SCAN	
A variety of package options	; (SQFP, LQFP, HQFP, PBGA, EBGA, IAB-BGA, FBGA)

Note: Some items are in preparation.

### Number of gates used in each package

The table below lists the available package types and the reference number of gates used. CE71 (J-Frame)

Package and pin count		0 1000 K 2000 K 3000 K 4000 K 5000 K	Material
	176		Р
SQFP	208		Р
	240	714 K	Р
	208	1313 K	Р
HOEP	240		Р
nori	256		Р
	304		Р
PBGA	256	——— 457 К	Ρ
	352		Р
EBGA	420		Р
	576	1986 K	Р
	660	5345 K	Р
	672	2673 K	Р

P: Plastic

CE71 (L-Frame)



Note: This list contains packages under planning. P: Plastic

#### CE71 (T-Frame)

Package and pin count		0 1000 K 2000 K 3000 K 4000 K 5000 K	Material
	144	341 K	Р
	176	477 K	Р
LQFF	208	1014 K	Р
	256	1358 K	Р
	208		Р
	240		Р
	256	1559 K	Р
	304		Р
	144	341 K	Р
	176	477 K	Р
FDGA	224		Р
	288	1559 K	Р
PBGA	256		Р
	352	1976 K	Р
	420		Р

Note: This list contains packages under planning.

P: Plastic

## CE66 Series

## Features

outuroo	
High integration	: Maximum of 1,138,000 BCs
Technology	: 0.35 $\mu$ m Si-gate, 3- to 4-layer metal wiring
Supply voltage	$\pm +3.3 \text{ V} \pm 0.3 \text{ V}$ (normal) to $\pm 2.0 \text{ V} \pm 0.1 \text{ V}$
	+5.0 V $\pm$ 10% (only for external interface; when internal requirements is 3.3 V)
	+3.3 V $\pm$ 10% (only for external interface; when internal requirements is 3.3 to 2.0 V)
Gate delay time	: t <sub>nd</sub> = 98 ps (high-speed type, F/O = 2, standard load)
Gate power consumption	$0.29 \mu W/MHz$ (F/O = 2, standard load)
Junction temperature range	: - 40 to 125°C
High-load driving capability	: $I_{OL} = 2 \text{ mA}/4\text{mA}/8\text{mA}/12\text{mA}/24\text{mA}$ mixable.
Output buffer cells with noise	e reduction circuits
On-chip input pull-up/pull-do	wn resistors (50 kΩ typical)
Buffer cells dedicated to crys	stal oscillator
Configurable internal bus cir	cuits
Highly integrated RAM/ROM	I/multipliers mountable; arbitrary words/bits configurable.
Clock skew layout design me	ethod (CDDM) based on the floor plan information minimizes post-layout circuit modifica-
tion, reducing turnaround tin	ne for development.
Simulation (before layout) co	onsidering the input through rate and detailed RC delay calculation (after layout),
supporting development with	n minimized timing trouble after trial manufacture.
Special interfaces (T-LVTTL	and SDRAM-I/F, and others)
Analog PLL	
Analog circuits (ADC, DAC,	OPAMP and others)
Macros for system ASICs (C	PU core, CPU peripheral, operational macros, and others)
Supports DFF scan test with	n MUX
Supports memory (RAM/RC	νΜ) SCAN
Supports memory (RAM) BI	ST
Supports boundary SCAN	

Number of gates used in each package The table below lists the available package types and the reference number of gates used. CE66 (P-frame)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K 1	100K 1200K
TQFP	100		—— 1138K
LQFP	100 144 176 208	939K	1138K 1138K 1138K
QFP	120 144 160 176 208 240 256		1138K 1138K 1138K 1138K 1138K 1138K 1138K 1138K 1138K
HQFP	208 240 256 304		1138K 1138K 1138K 1138K 1138K
PBGA	256 352		1138K 1138K
FBGA	112 144 168 176 192 224 288	459K 459K 939K	—— 1138K —— 1138K —— 1138K

Note: This list contains packages under planning.

#### CE66 (S-frame)

Package and pin count		0 50K 100K 150K 200K 250K 300	)K 350K 400K 450K 500K 550K 600K
TQFP	100	——— 112К	
LQFP	100 144 208	112K 112K	— 311K
QFP	120 144 160 176 208 240	112K 112K 163K 163K 256K	390К
HQFP	208 240 256	256K	
PBGA	256 352		390K 579K
FBGA	112 144 168 176 192 224 288	136K 163K 163K 206K	– 311K – 311K – 579K

## CE61 Series

### Features

catalos	
High Integration	: Maximum of 2,000,000 BCs
Technology	: 0. 35 $\mu$ m Si-gate 3-layer metal wiring/4-layer metal wiring
	(There are restrictions applicable frames)
Basic circuit (basic cell)	: 2-input NAND/2-input NOR gates
Supply voltage	: +3.3 V $\pm$ 0.3 V (normal) to +2.0 V $\pm$ 0.1 V
	High voltage tolerant transistor for I/O; interface provided for 5 V devices
	(Also requiring a 5 V power supply for interface with 5 V devices)
Gate delay time	: High-speed type, t <sub>pd</sub> = 85 ps (2-input NAND, F/O = 2, standard load)
Junction temperature range	: 0 to +100°C
High-load driving capability	: I <sub>OL</sub> = 2 mA/4 mA/8 mA/12 mA/24 mA mixable.
Power consumption	: Reduced to 50% to 20% (over the CE51 Series)
Output buffer cells with noise	e reduction circuits
On-chip input pull-up/pull-do	wn resistors (Typ. 50k $\Omega$ )
Buffer cells for crystal oscilla	tion circuits.
Configurable internal bus cir	cuits
Super high-integration RAM	and ROM available. Compilable bit/word configuration
Clock skew reduction layout ing TAT	design technique (CDDM) employed to minimize circuit modification after layout, reduc-
Simulation (before layout) co supports development with r	nsidering the input through rate and detailed RC delay calculation (after layout), ninimized timing trouble after trial manufacture.
Supports high speed interfac	ces [P-CML (200 MHz transmission), LVDS (250 MHz transmission), and SDRAM I/F,
PCI,5 V tolerant, USB, IEEE	1284]
PLL circuits	
Analog circuits (ADC, DAC)	
Macros for system ASICs (C	PU core and CPU peripheral and operational macros, and others)
Supports tests (for function/I	C) using DFF scan with MUX
Supports the test for RAM B	IST, RAM SCAN and ROM SCAN
Supports the Boundary SCA	N
Now under preparation on fo	r a narrow-pitch pad technology and high-pin count BGA packages to be added to the
Variety of package options to	o ontimize any gate size
vallely of package options to	oplimize any gale size

### Number of gates used in each package)

The table below lists the available package types and the reference number of gates used."

CE61 (F10 to F80)

Package and pin count		0 100K 200K 300K 400K 500K 600K 700K 800K 900K 1000K1100K1200K1300K	Material
QFP	64 80 100 120 144 160 176 176 208 208 240 240 256 256 304	86K         86K         86K         86K         981K         1317K         1317K	Р
LQFP	64 80 100	енерокание и век век век век	P P P
HQFP	208 240 256 304	981K 1317K 981K 1317K 981K	P P P P
BGA	256 352 420	593K981K	P P P
PGA	256 299 361 401		С С С С

P: Plastic C: Ceramic

Note: This list contains packages under planning.

CE61 (E7 to E71)



P : Plastic

## CG61 Series (Analog PLL embedment is possible in some frames)

#### **Features**

High Integration	: 1,560,000 BCs		
Technology	: 0. 35 µm Si-gate CMOS, 3-layer metal wiring		
Basic circuit (basic cell)	: 2-input NAND/2-input NOR gates		
Supply voltage	: +3.3 V $\pm$ 0.3 V (normal) to +2.0 V $\pm$ 0.1 V		
	(5 V TTL interface is possible when 5 V tolerant I/Os are used.)		
Gate delay time	: t <sub>pd</sub> = 85 ps (3.3 V, 2-input NAND, F/O = 2, standard load)		
Gate power dissipation	: 0.24 $\mu$ W/MHz (2.0 V, 2-input NAND, F/O = 2, standard load)		
Junction temperature range	: 0 to +100 °C		
High-load driving capability	: I <sub>OL</sub> = 2 mA/4 mA/8 mA/12 mA/24 mA mixable		
Output buffer cells with noise	e reduction circuits		
On-chip input pull-up/pull-do	wn resistors (Typ. 50 k $\Omega$ <at 3.3="" v="">)</at>		
Buffer cells for crystal oscilla	Buffer cells for crystal oscillation circuits		
Configurable internal bus cir	cuits		
Compiled RAM can be embe	edded. Compilable bit/word configuration		
An analog PLL can be embe	added in CG61P only.		
Clock skew reduction layout d	esign technique (CDDM) employed to minimize circuit modification after layout, reducing TAT		
Simulation (before layout) co	onsidering the input through rate and detailed RC delay calculation (after layout),		
supports development with i	ninimized timing trouble after trial manufacture.		
Supports high speed interna	ces (I-LVIIIL, P-GML, LVDS, SDRAMI/F)		
Supports tests using DFF SC			
Supports the test for RAM B			

Number of gates used in each package The table below lists the available package types and the reference number of gates used.

CG 61 (The frame which cannot use Analog PLL)

Packa pin c	ge and count	0 100K 200K 300K 400K 500K 600K 700K 800K 900K	Material
LQFP	120	222K	P
	144	222K	P
QFP	240	222К	P
	256	395К	P
HQFP	208 240 256 304	580K 802K	P P P P

P: plastic

Note: This list contains packages under planning.

#### CG 61P (The frame which can use Analog PLL)

Pack an pin c	age d ount	0 20K 40K 60K 80K 100K 120K 140K 160K 180K 200K	Material
LQFP	48 64 100 120 144 176 208	16K 88K 188K 188K 188K 188K 188K 188K	P P P P P P
QFP	240	188К	P
	256	188К	P
BCC	48	88К	P
	64	88К	P

P: plastic

## CG47 Series

#### Features

outaioo	
High integration	: Maximum 55,000 BCs (on chip)
Technology	: 0.65 μm Si-gate CMOS, 2-layer metal wiring
Gate delay time	: 300ps (power type 2-input NAND, standard load)
Supply voltage	: [Single power supply] $+5 V \pm 5\%$ (normal), $+3.3 V \pm 0.3 V$ (normal)
	[Dual power supply] Internal domain: $+3.3 V \pm 0.3 V$ , $+5 V \pm 5\%$ (cannot be mixed)
	$1/0: +3.3 V \pm 0.3 V, +5 V \pm 5\%$ (can be mixed)
Interface enabled betw	veen dual power sources
Low power consumption	on enabled by operating internal supply voltage at 3.3V.
Delay time estimation	by detailed time equations
Detailed time equation	s can be used for the estimation of delay time closer to that of actual devices.
Buffer cells for crystal	oscillations circuits
Supports separate low	r frequency (32 kHz), and high frequency (1 to 40MHz) buffers, and oscillator stop function.
Supports output open	drain cell and input fail safe cells
Compiled cells include	aingle part PAM, dual part PAM, and EIEO memory

Compiled cells include single port RAM, dual port RAM, and FIFO memory.

Note: The type of the RAM that can be used is specified depending on the internal power supply when the RAM is a single-port RAM.

HISCAN (scan circuit automatic generation function)

HISCAN is supported with single power supply, but dual power supply specifications and HISCAN are mutually exclusive.

Simple interface

CAD-to-CAD interface uses special language for logic data (FLDL) and test data (FTDL).

Integrated development tools

### Number of gates used in each package

The table below lists the available package types and the reference number of gates used.

Package and pin count		0 5K 10K 15K 20K 25K 30K 35K 40K 45K 50K
SSOP	30	— 2К
LQFP	48 64 80 100 120 144 176 208	11K 21K 33K 33K 33K 33K 33K 33K
QFP	64 80 100 240	21K 21K 21K 21K 33K
BCC	48 64 80	21K 31K 31K

# Sea-of-Gate Type CMOS Gate Arrays

## CG46 Series

## Features

High integration	: Maximum 198,08	84 BCs (on chip)					
Technology	: 0.65 μm Si-gate CMOS, 2-layer metal wiring						
Basic circuit (basic cell)	: 2-input NAND/2-	input NOR gates					
Input level	: TTL/CMOS level	mixable					
Supply voltage	: +5 V ± 5% (norm	nal)					
	+3.3 V ± 0.3 V (c	optional)					
Gate delay time	: Standard gate	tpd = 360 ps (2-input NAND, standard load)					
	Power gate	tpd = 300 ps (2-input NAND, standard load)					
Operating temperature	: 0 to +70°C						
High-load driving capability	: I <sub>OL</sub> = 3.2 mA/8 m	A/12 mA/24 mA mixable					
Output buffer cells with nois	e reduction circuits						
On-chip input pull-up/pull-do	own resistors (Typ. 5	50 kΩ)					
Buffer cells for crystal oscilla	ations circuits						
Configurable internal bus cir	rcuits						
RAM and FIFO memory allo	owing arbitrary bit/w	ord configuration					
Clock skew reduction layout	design technique (	CDDM) employed to minimize circuit modification after layout, reduc-					
ing the period of time for dev	ing the period of time for development						
Delailed RC delay calculation minimized timing trouble after trial manufacture.							
Supports ATG (Automatic Test Generation) based on scan design							
Supports HISCAN (automat	ic scan generation)						
Simplified interface: CAD-to	-CAD interface use	s special language for logic data (FLDL) and test data (FTDL).					
Integrated development tool	S						

Number of gates used in each package The table below lists the available package types and the reference number of gates used.



## ■ Package Line-up

The packages are classified as follows, according to form, material, and the mounting methods for which they are suited.



Name of package Description		Lead pitch (mm)	
PGA	Pin Grid Array Package	1.27/2.54	
SOP	Small Outline Package (straight lead) Small Outline L-Leaded Package	1.27	
SOL <sup>*2</sup>	Small Outline L-Leaded Package (JEDEC*1)	1.27	
SSOP	Shrink Small Outline L-Leaded Package	0.65/0.80/1.00	
TSOP (I)	Thin Small Outline L-Leaded Package (I)	0.50/0.55/0.60	
TSOP (II)	Thin Small Outline L-Leaded Package (II)	0.50/0.80/1.00/1.27	
SON	Small Outline Non-Leaded Package	0.50/1.00	
QFP	Quad Flat Package (straight lead) Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80/1.00	
LQFP*2	Low-Profile Quad Flat L-Leaded Package	0.40/0.50/0.65/0.80	
TQFP	Thin Quad Flat L-Leaded Package	0.40/0.50	
HQFP	QFP with Heat Sink	0.40/0.50/0.65	
LCC <sup>*2</sup>	Leadless Chip Carrier	1.010/1.07	
QFN	Quad Flat Non-Leaded Package	1.016/1.27	
BGA	Ball Grid Array	1.27/1.0	
FBGA	Fine pitch Ball Grid Array	0.8/0.75/0.65/0.5	
DTP	Dual Tape Carrier Package	_	
QTP	Quad Tape Carrier Package	_	

\*1: Joint Electron Device Engineering Council

\*2: Package name used by Fujitsu Microelectronics

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